

**ROCHESTER INSTITUTE OF TECHNOLOGY  
MICROELECTRONIC ENGINEERING**

**PMOS Testing  
at  
Rochester Institute of Technology**

**Dr. Lynn Fuller**

webpage: <http://www.rit.edu/~lffeee>

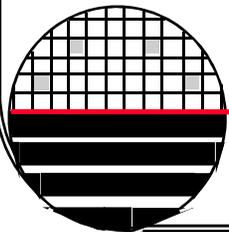
**Microelectronic Engineering  
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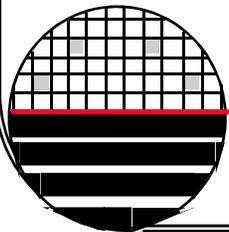
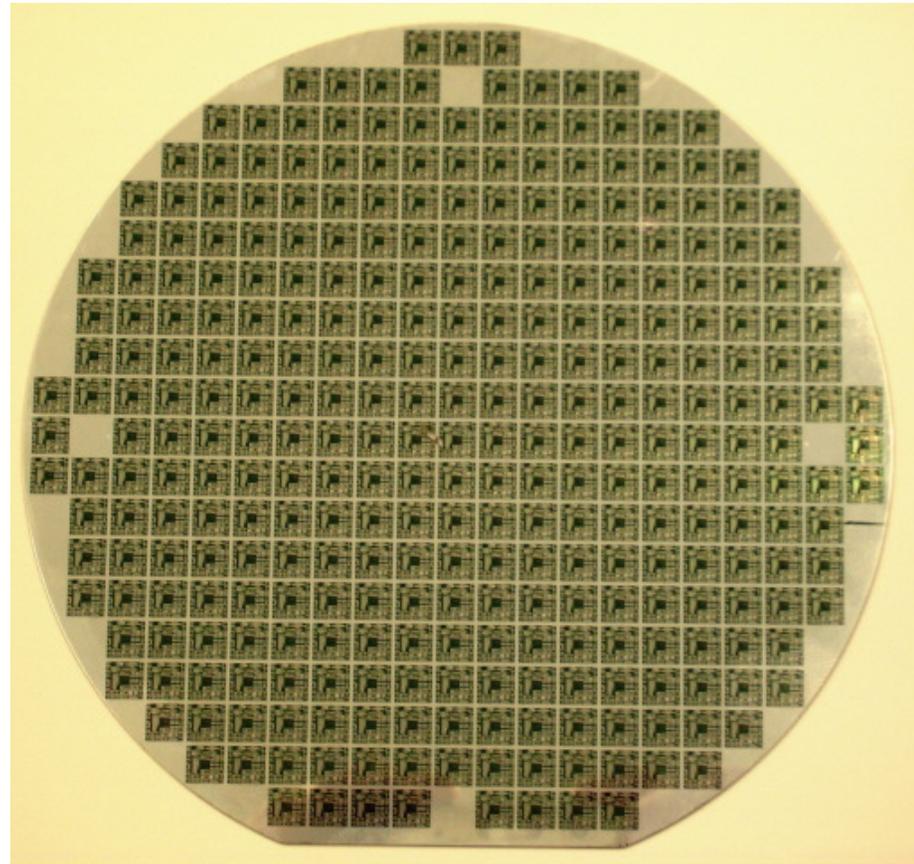


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**Revised 11-11-2010 pmostest.ppt**

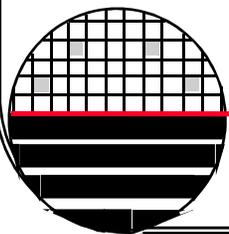
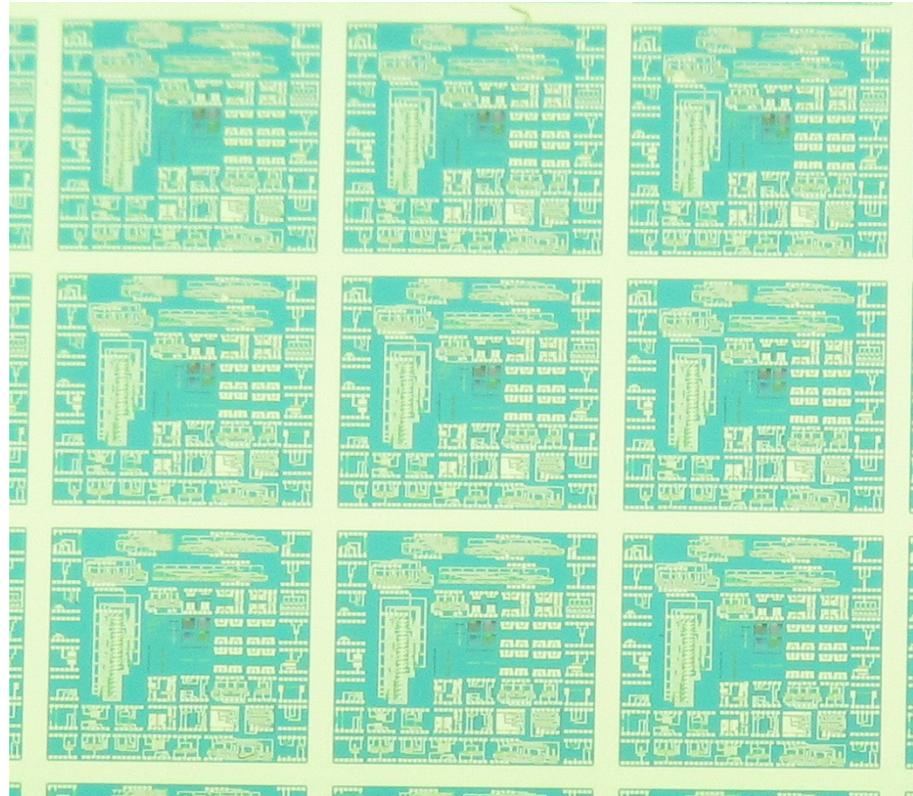
**OUTLINE**

- **Test Chip**
- **Test Equipment**
- **Resistive Structures**
- **Transistors**
- **Integrated Circuits**
- **Ring Oscillator**
- **Digital Circuits**

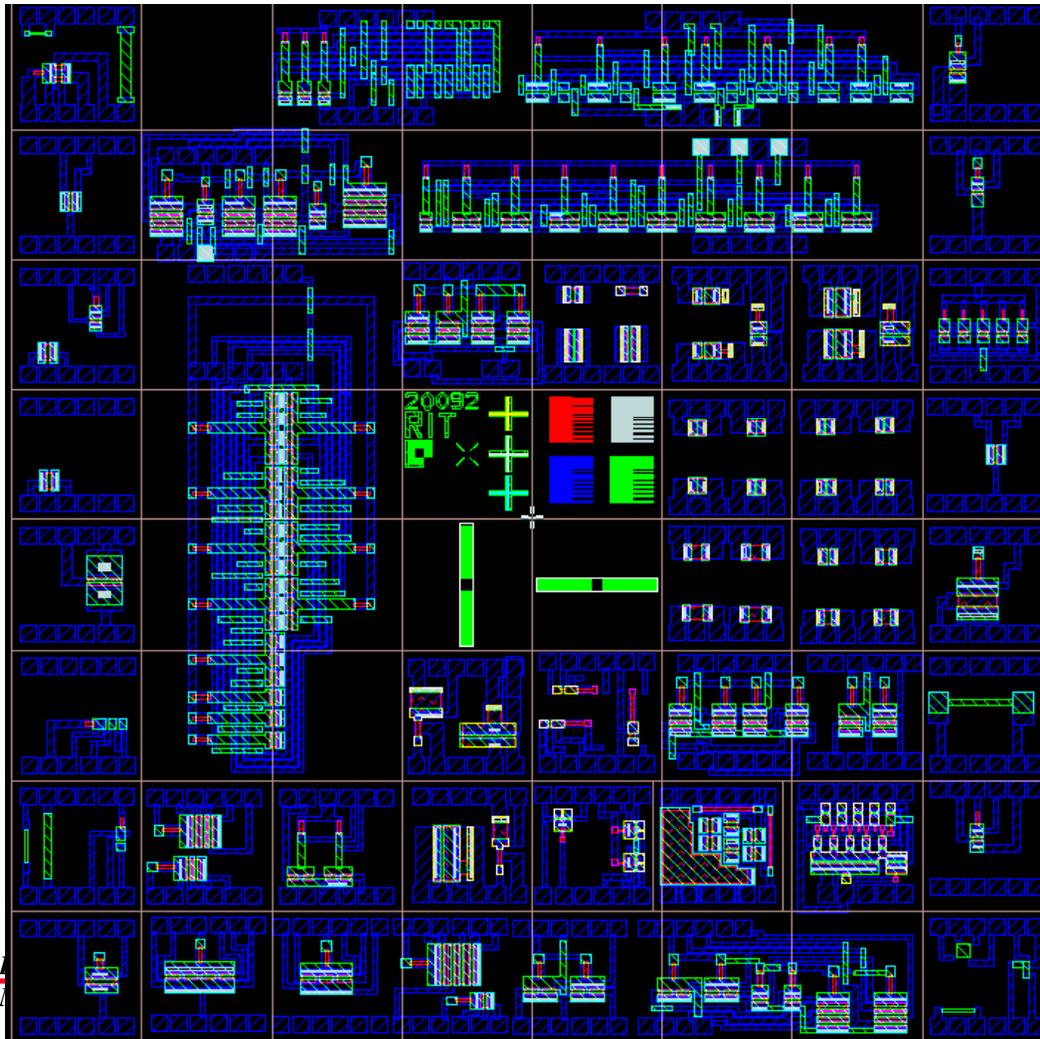


## THE TEST CHIP

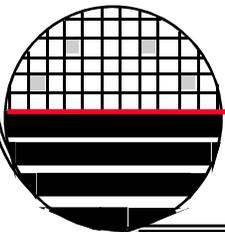
- Alignment Marks
- CD Linewidth, Overlay
- Van Der Pauw, p+ DS, Metal
- MOSFET's,
- Inverters
- Ring Oscillator
- CBKR
- Digital Circuits



*PMOS TEST CHIP*



Fall 2010

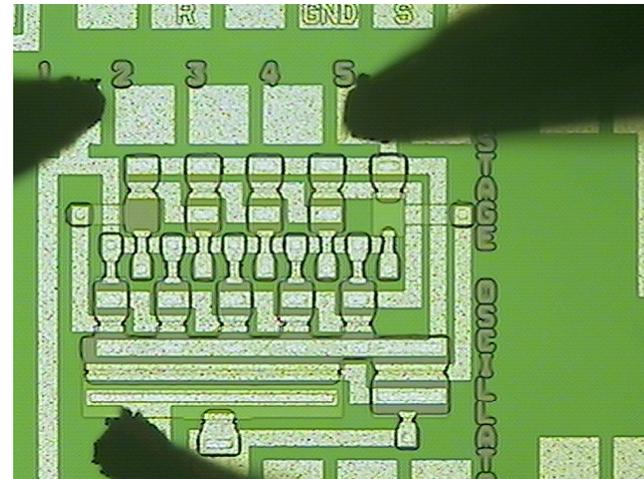


**TEST FACILITY**

 **HP4145  
Semiconductor Paramater  
Analyzer**

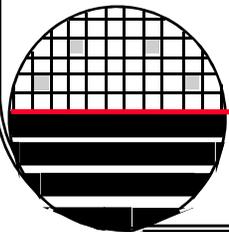
**Keithley  
7001 Switch Matrix**

**Computer  
ICS Software  
Camera**



**Ultracision  
Semi-Automatic  
Wafer Prober**

**Test Fixture  
and  
Manual Probe Station**



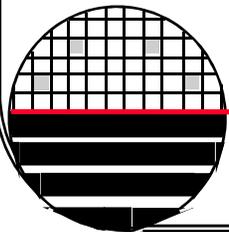
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**TEST EQUIPMENT**



Automatic Prober

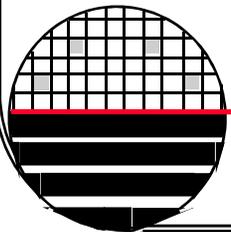
Semi-automatic Prober



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*TEST EQUIPMENT*

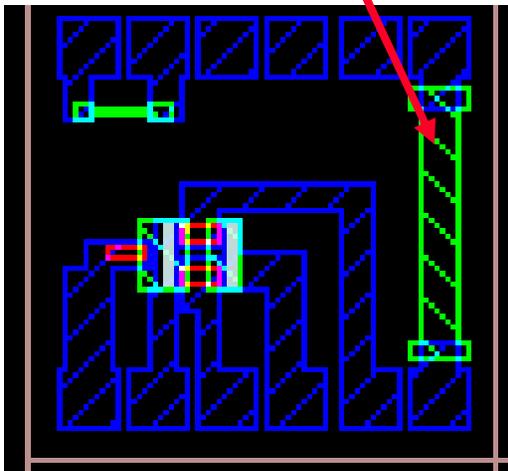
Manual Prober



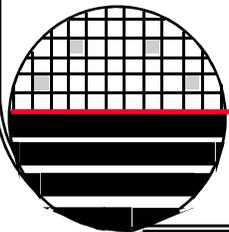
**RESISTOR TEST RESULTS**

$R = R_{hos} L/W$

$L/W = 400/60$

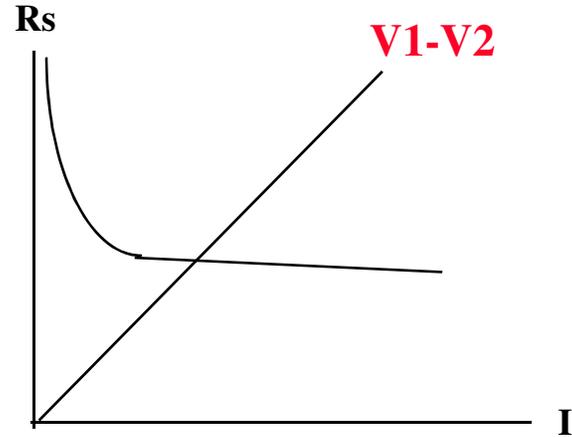
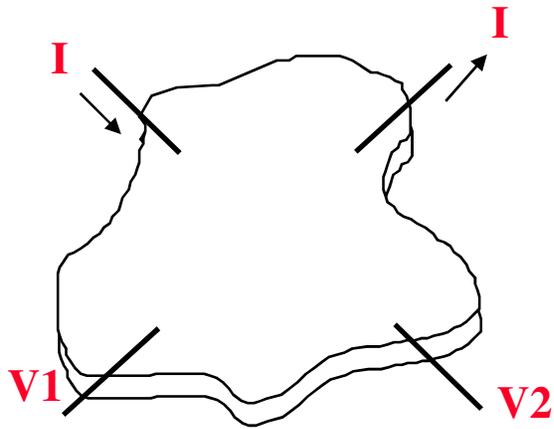


$R = V/I = 1/\text{slope}$   
 $= 647 \Omega$

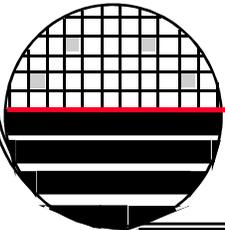
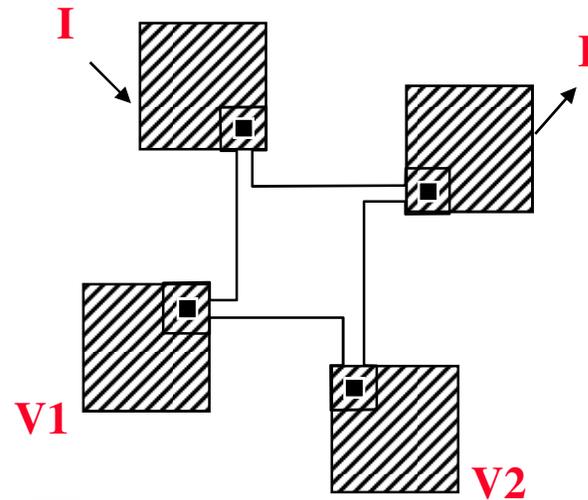


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**VAN DER PAUW TEST STRUCTURES FOR SHEET RESISTANCE**

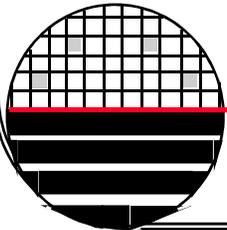
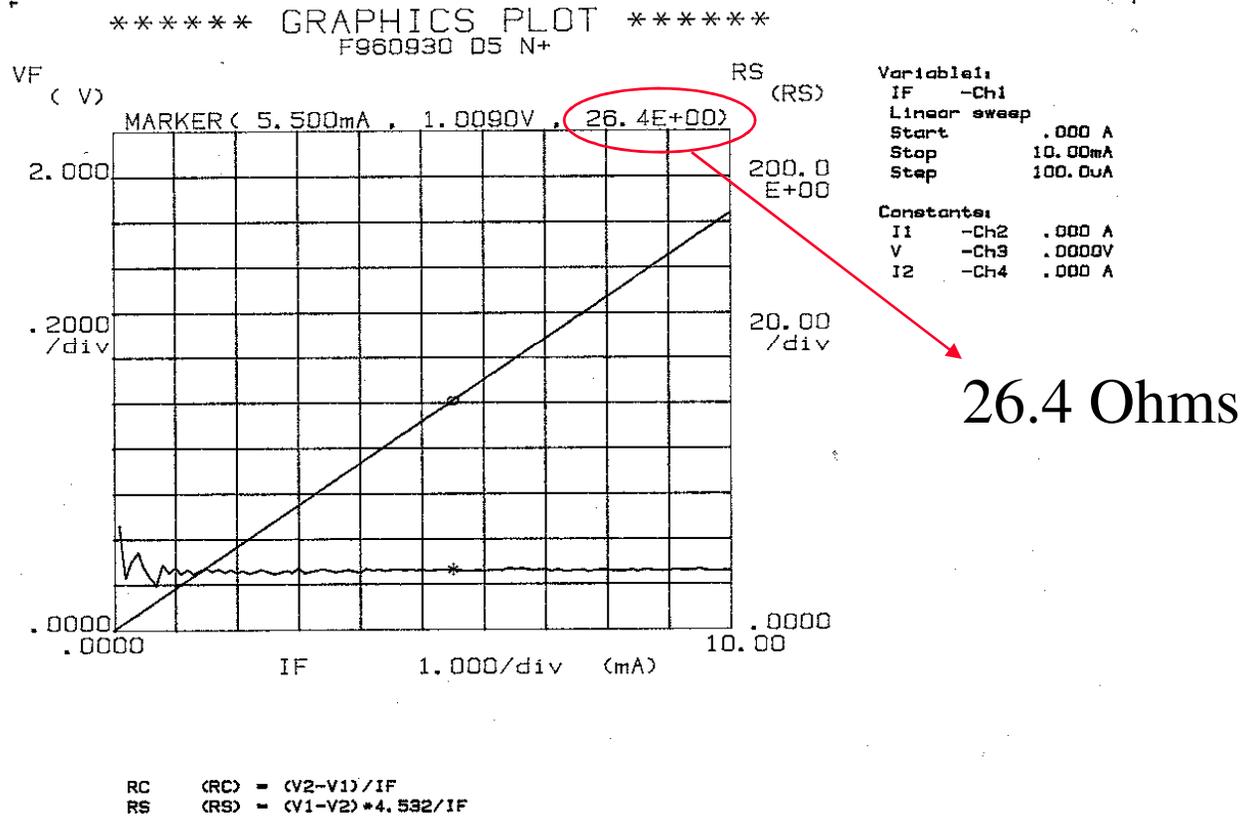


$$R_s = \frac{(V1-V2) \pi}{I \ln 2}$$

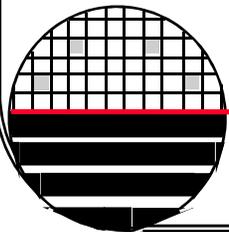
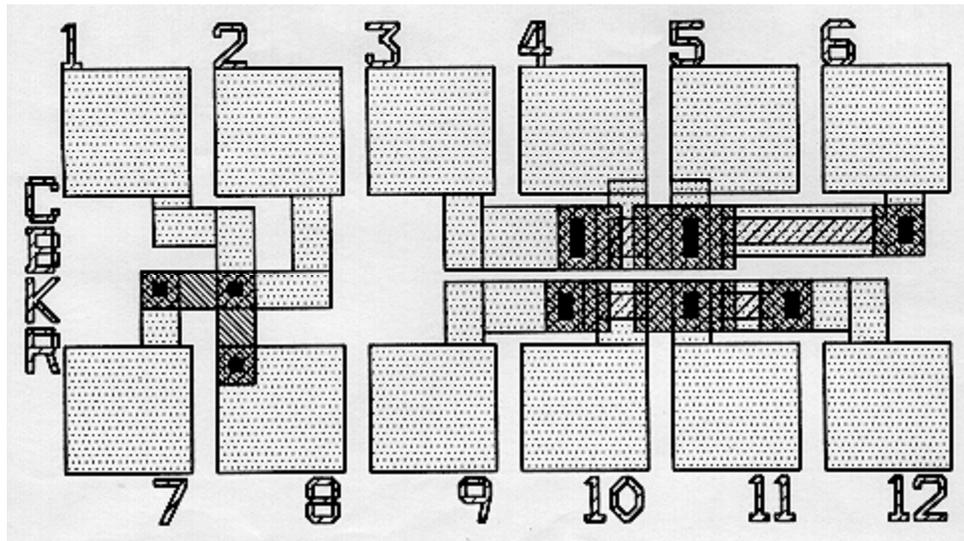


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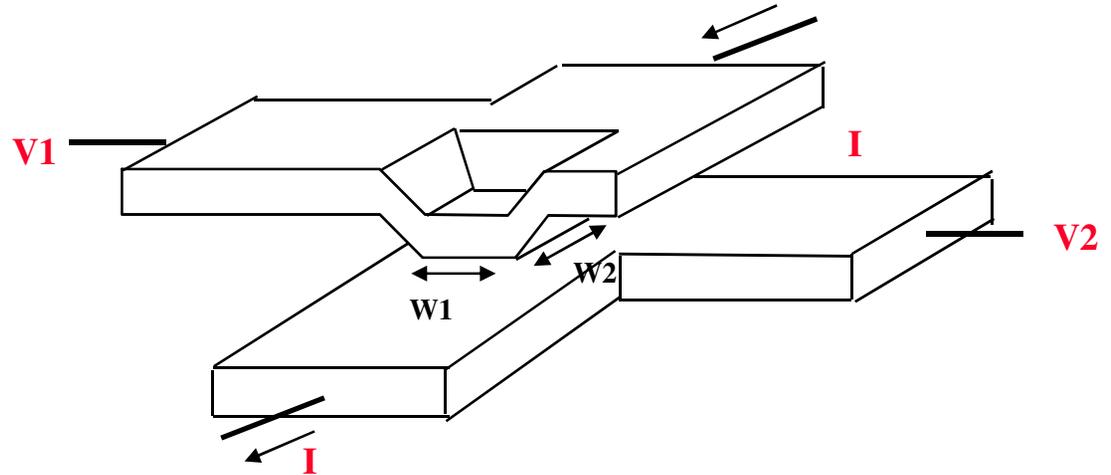
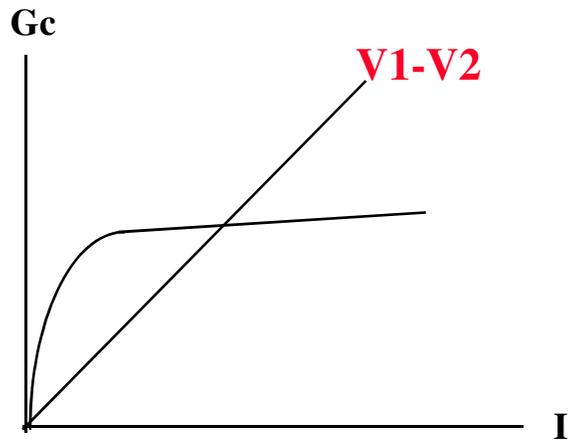
# VAN DER PAUW TEST RESULTS



**CBKR AND INVERTERS**

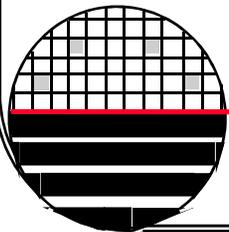


**CROSS BRIDGE KELVIN RESISTANCE TEST  
STRUCTURES FOR CONTACT RESISTANCES**

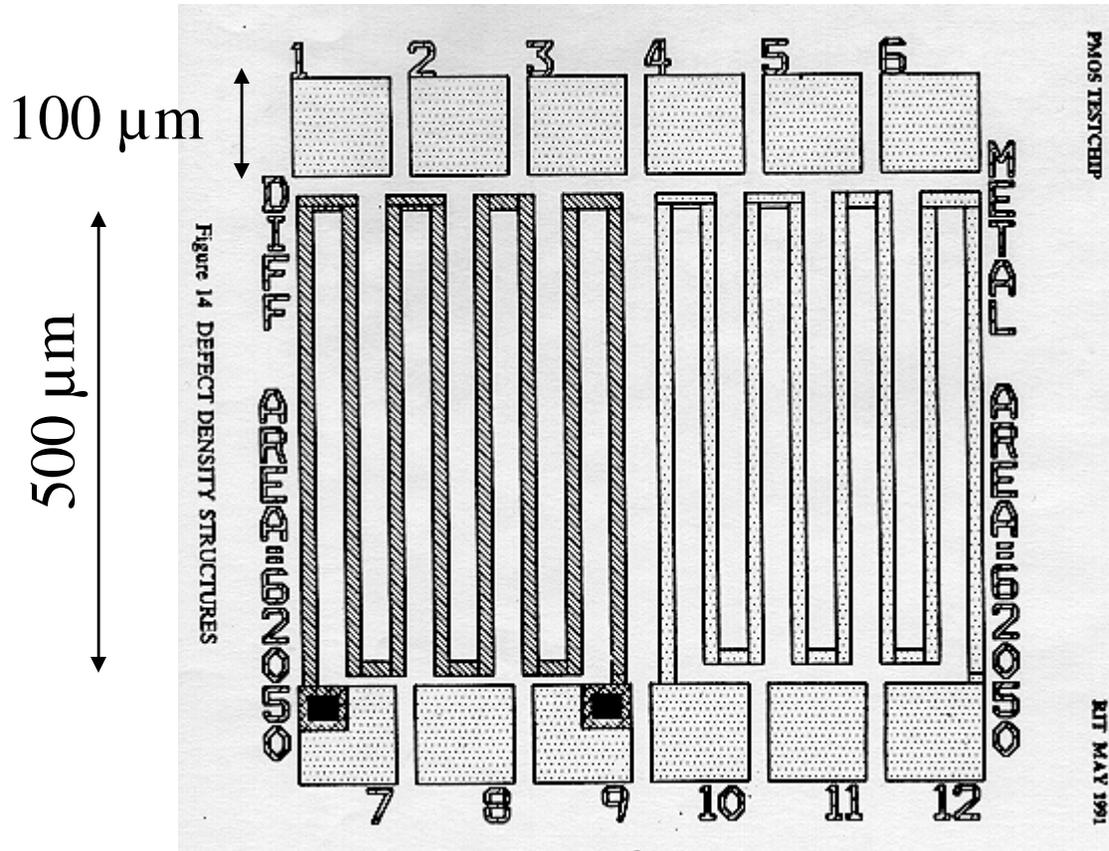


$$R_c = \frac{(V1-V2)}{I} \quad \text{ohms}$$

$$G_c = \frac{I}{(V1-V2)} = \frac{1}{W1 \times W2} \quad \text{mhos}/\mu\text{m}^2$$



**METAL AND DIFFUSION SERPENTINE**

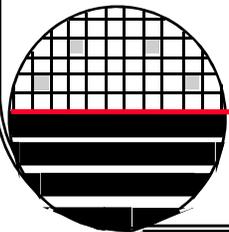


Line width = 15 μm  
 Line Space = 30 μm  
 L/W = 269  
 Area Covered by metal  
 = 62050 μm<sup>2</sup>

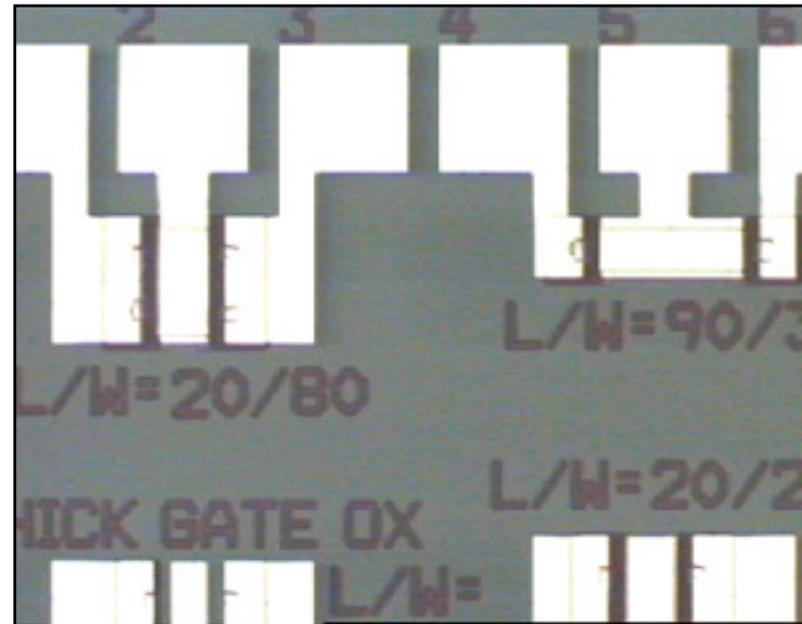
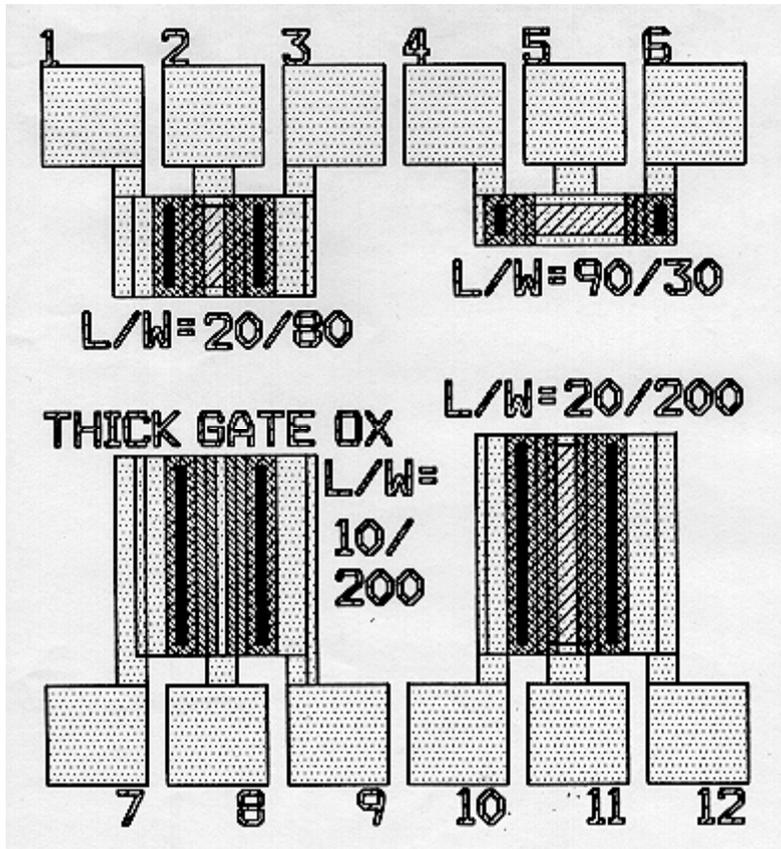
$$R = R_{hos} L/W$$

Defect density ( in #/cm<sup>2</sup> ) = (# defective x 1612) / (# tested)

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# PMOS TRANSISTORS

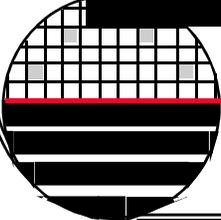
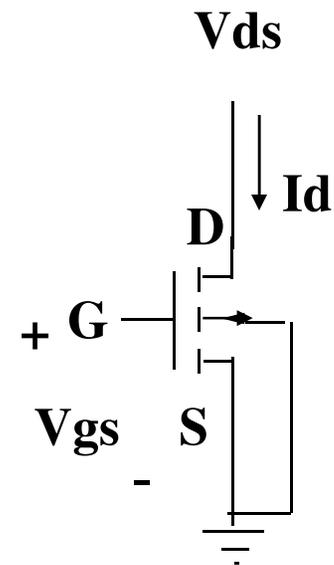
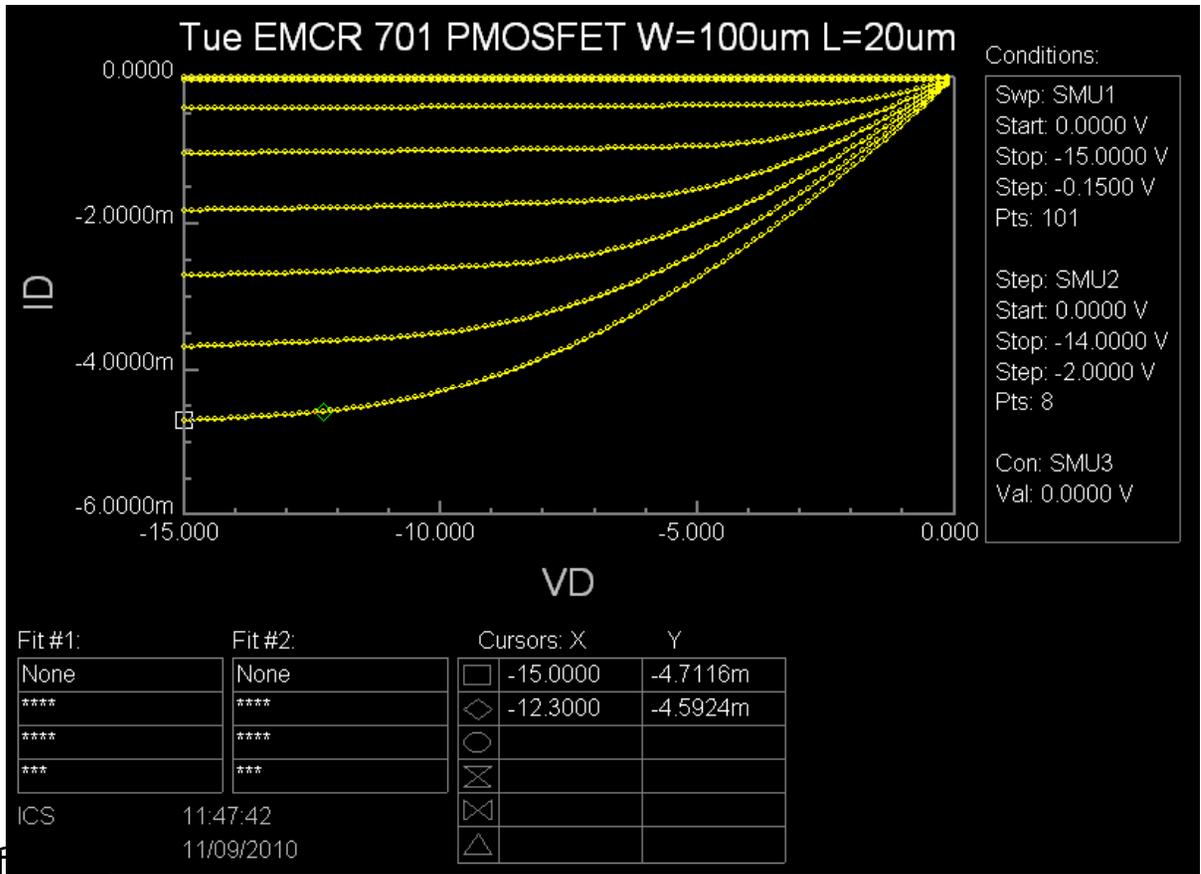


Layout

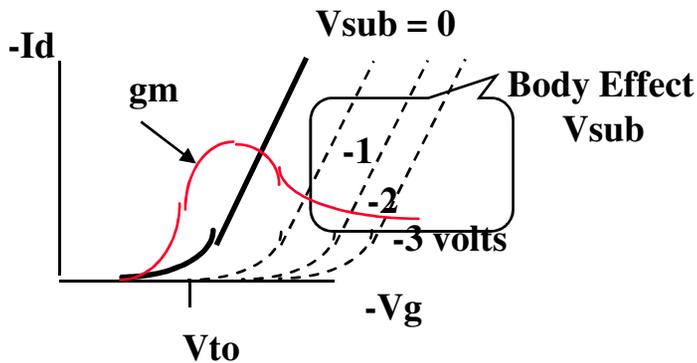
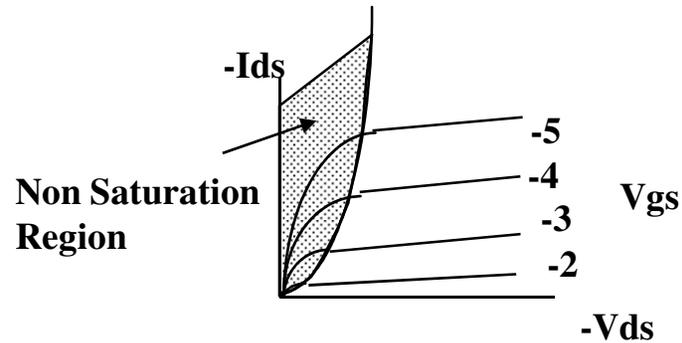
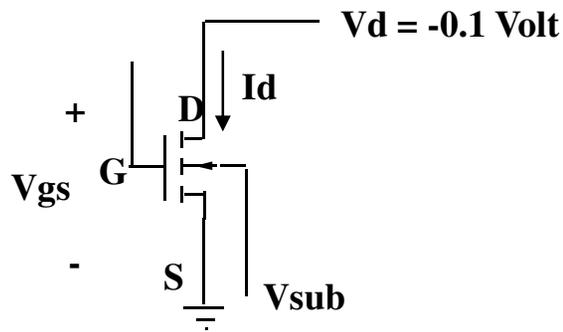
Photograph

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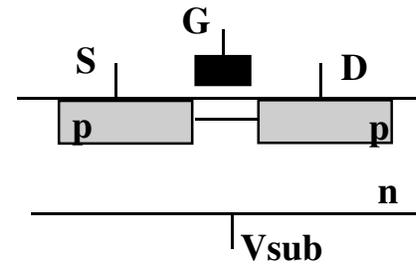
# PMOS TRANSISTOR TEST RESULTS



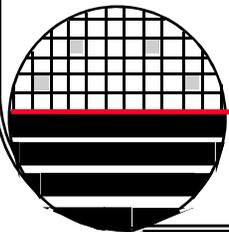
**TRANSISTOR LINEAR REGION  $V_t$ ,  $g_m$**



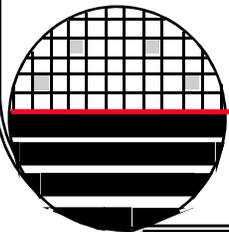
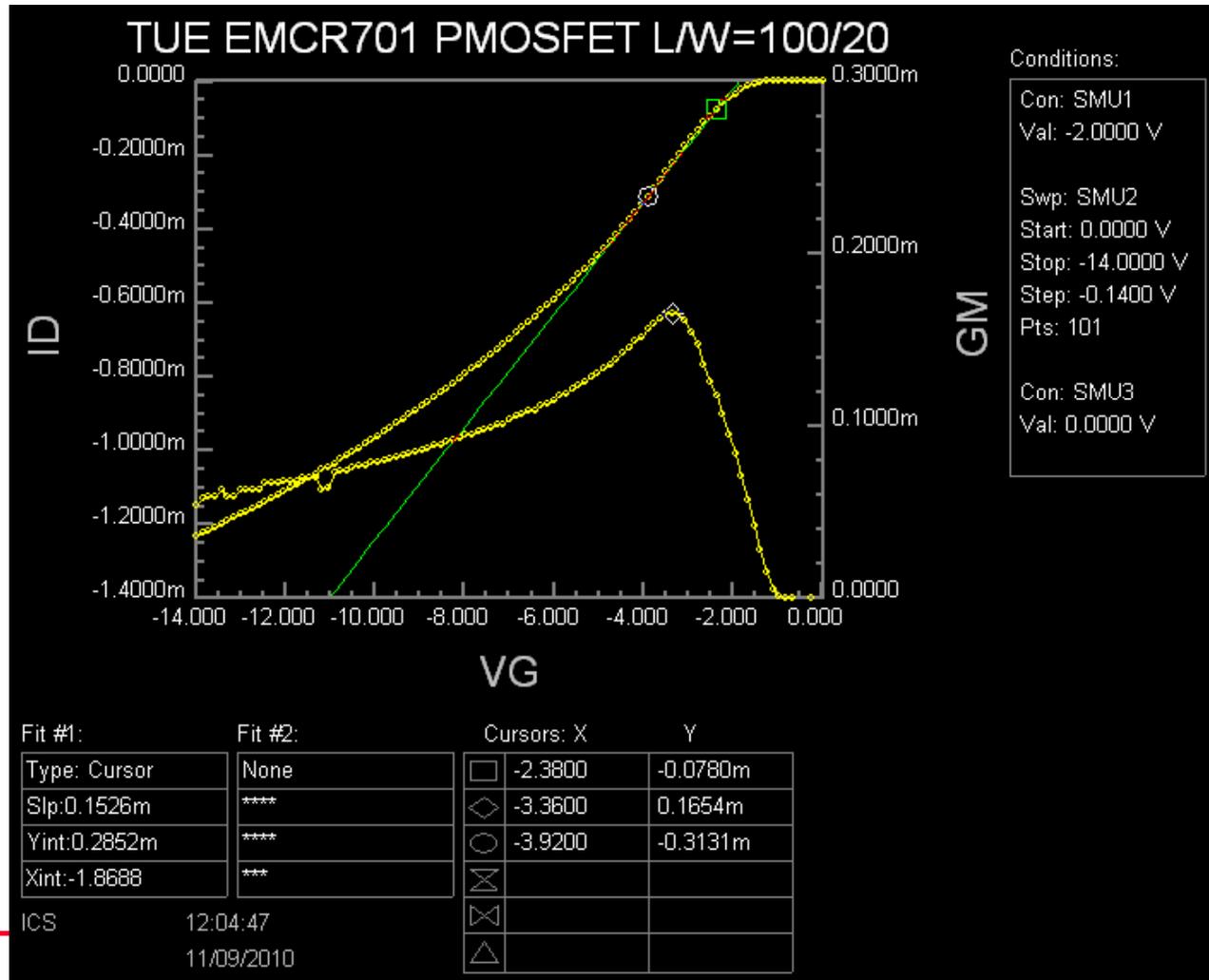
$$g_m = \Delta I_d / \Delta V_g$$



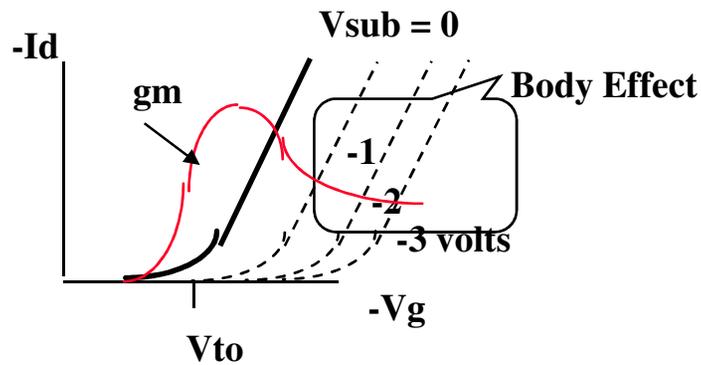
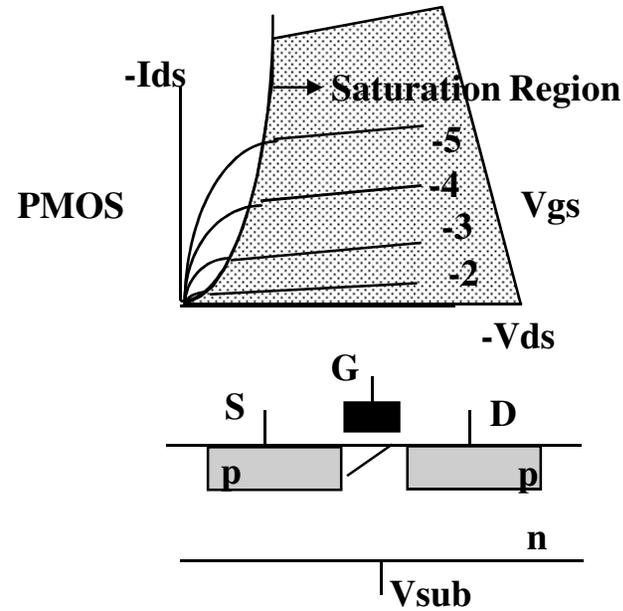
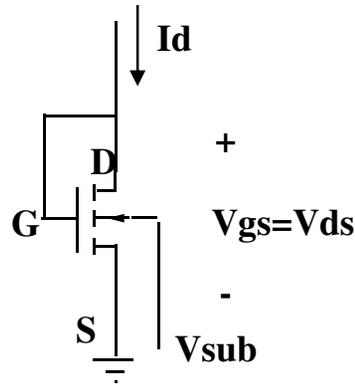
pMOSFET with  $V_t = -1$ , since the Drain is at  $-0.1$  volts and the source is at zero. Both drain and source will be on at gate voltages greater than  $-1.1$  volt. the transistor will be in the non saturation region.



**LINEAR REGION TEST RESULTS**



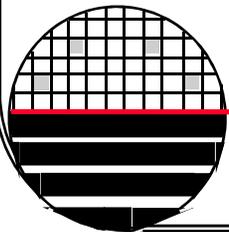
**TRANSISTOR SATURATION REGION  $V_t$ ,  $g_m$**



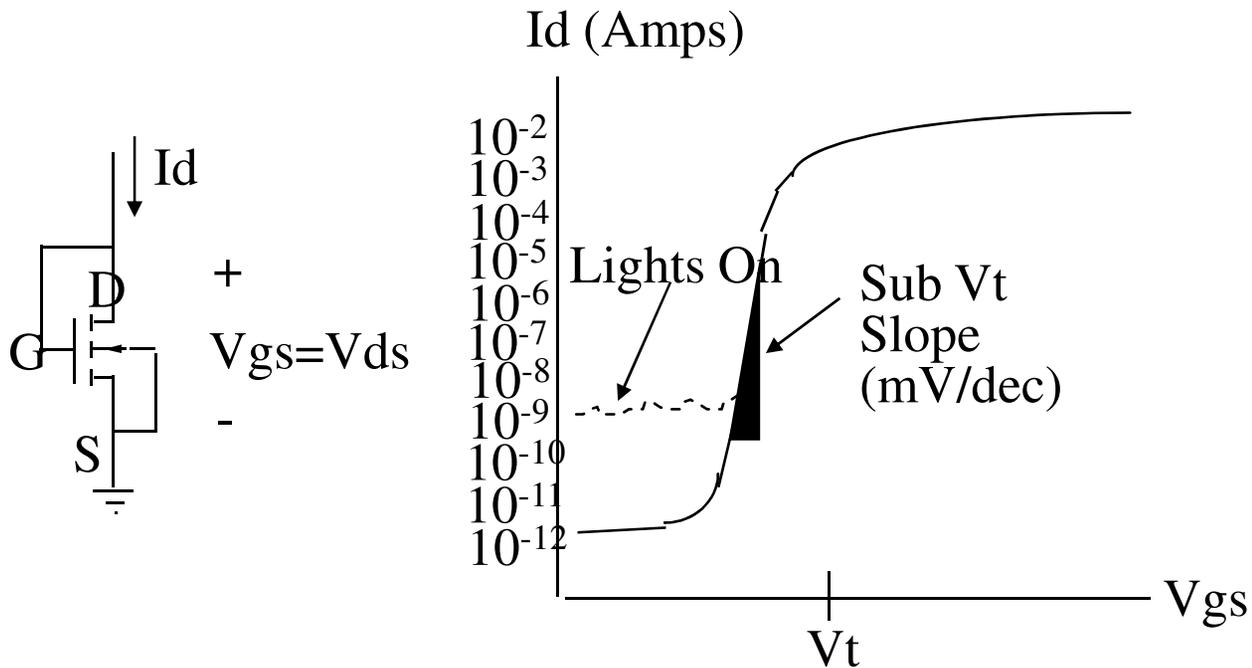
pMOSFET with  $V_t = -1$ , Drain end is never on because Voltage Gate to Drain is Zero. Therefore this transistor is always in Saturation Region if the gate voltage is above the threshold voltage.

$$g_m = \Delta I_d / \Delta V_g$$

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**TRANSISTOR SUB THRESHOLD  $I_D$ - $V_{GS}$**



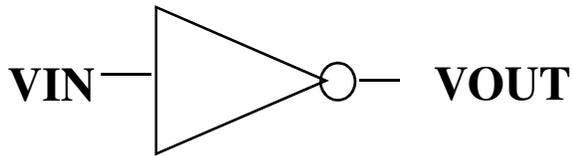
The subthreshold characteristics are important in VLSI circuits because when the transistors are off they should not carry much current since there are so many transistors. (typical value about 100 mV/decade)

# INVERTERS

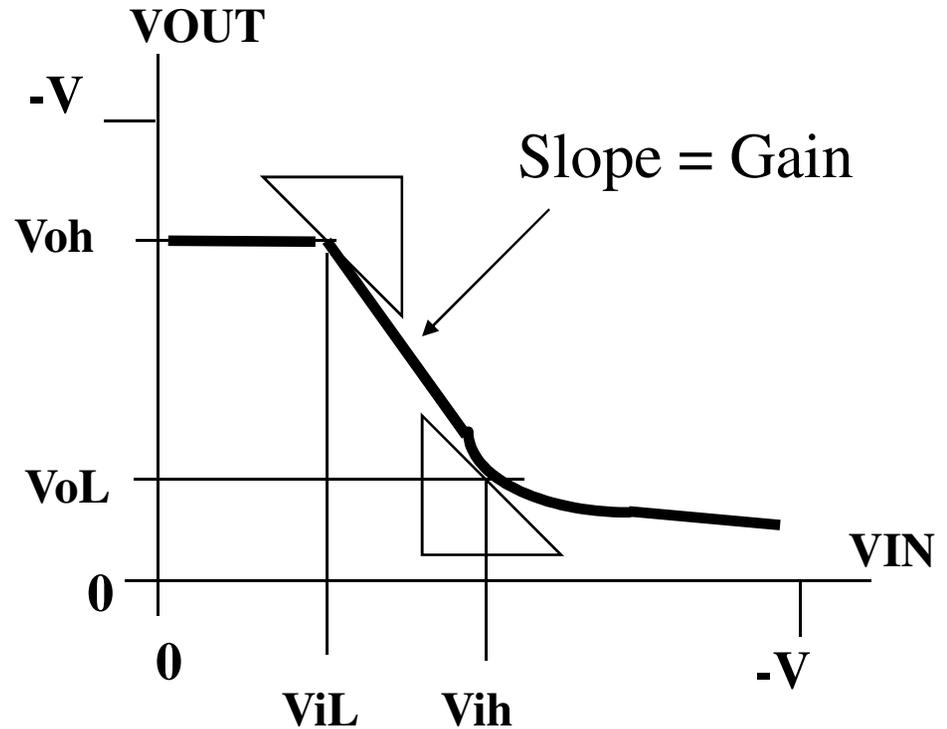
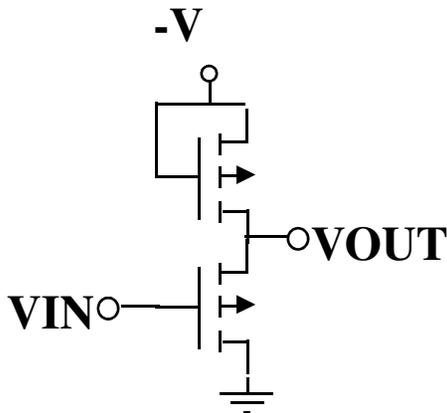


$L = 40\mu\text{m}$   
 $W = 20\mu\text{m}$   
 $L = 20\mu\text{m}$   
 $W = 50\mu\text{m}$

# INVERTERS



$$\text{Inverter Gain} = \sqrt{\frac{W_d/L_d}{W_u/L_u}}$$

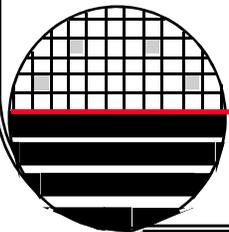


## PMOS Inverter with Enhancement Load

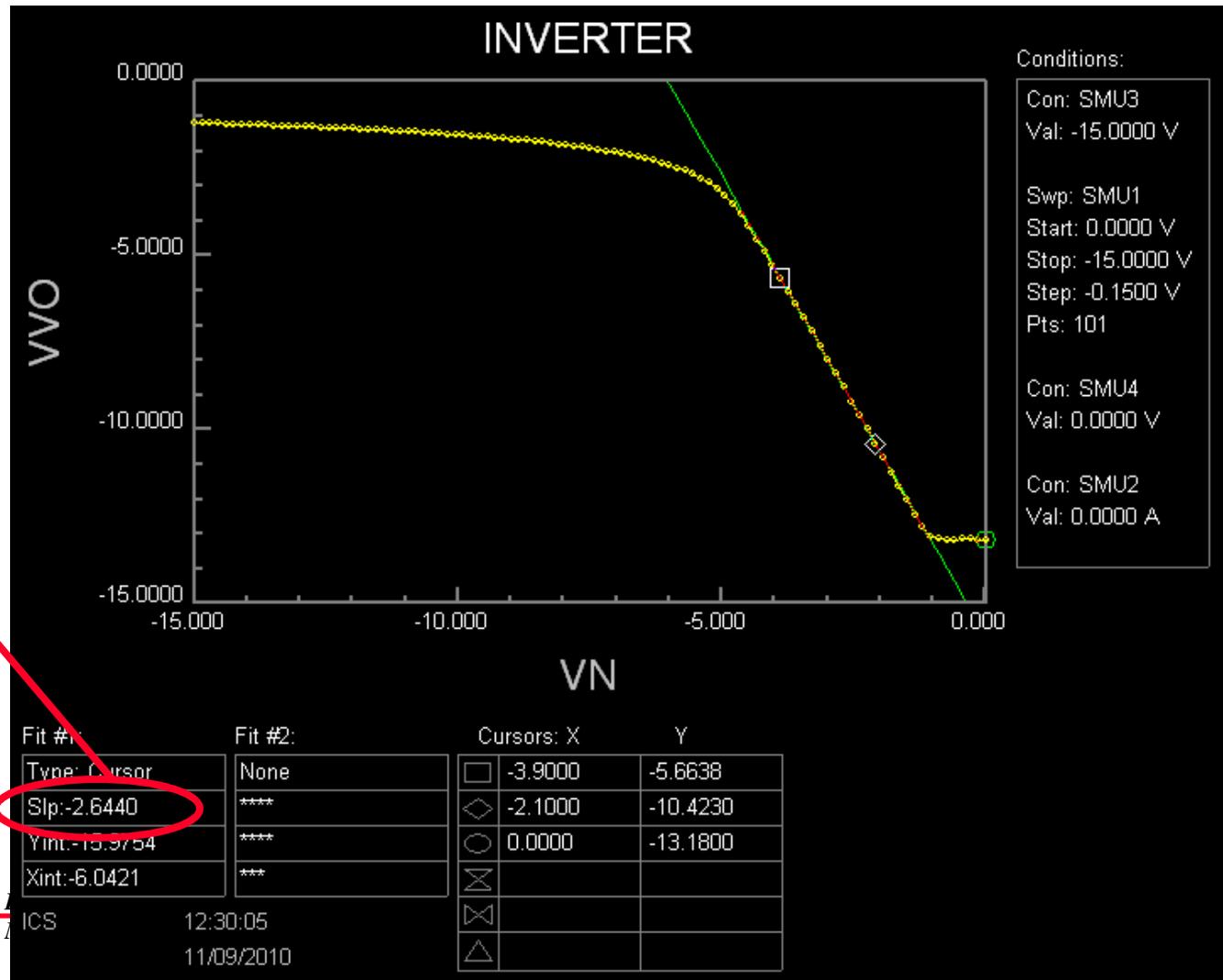
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$$\Delta 0 \text{ noise margin} = V_{iL} - V_{OH}$$

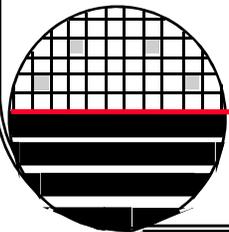
$$\Delta 1 \text{ noise margin} = V_{OH} - V_{iH}$$



# INVERTER TEST RESULTS



Gain = -2.64



**RING OSCILLATOR,  $t_d$**

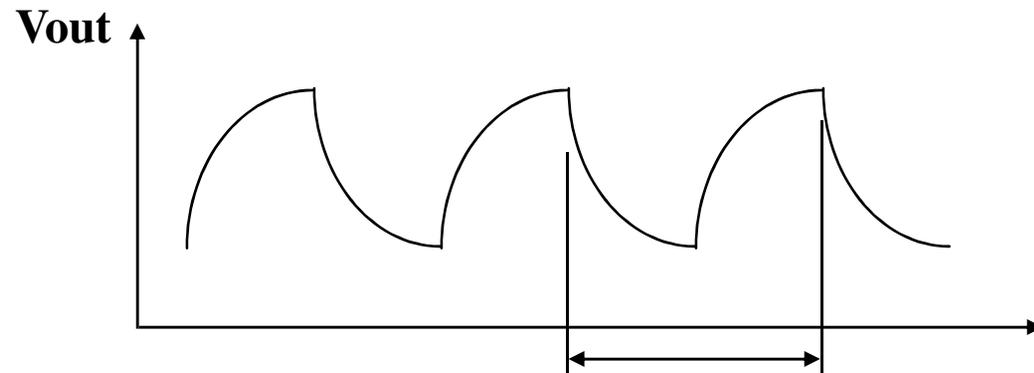
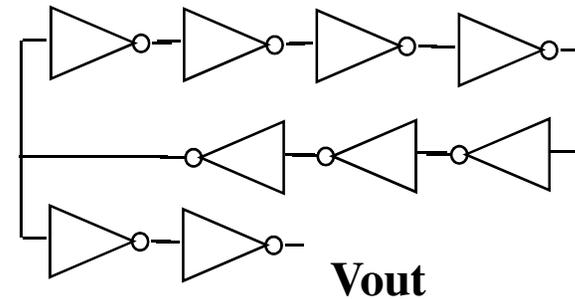
**Seven stage ring oscillator  
with two output buffers**

$t_d = T / 2 N$

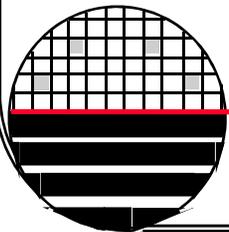
$t_d$  = gate delay

$N$  = number of stages

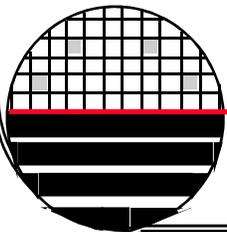
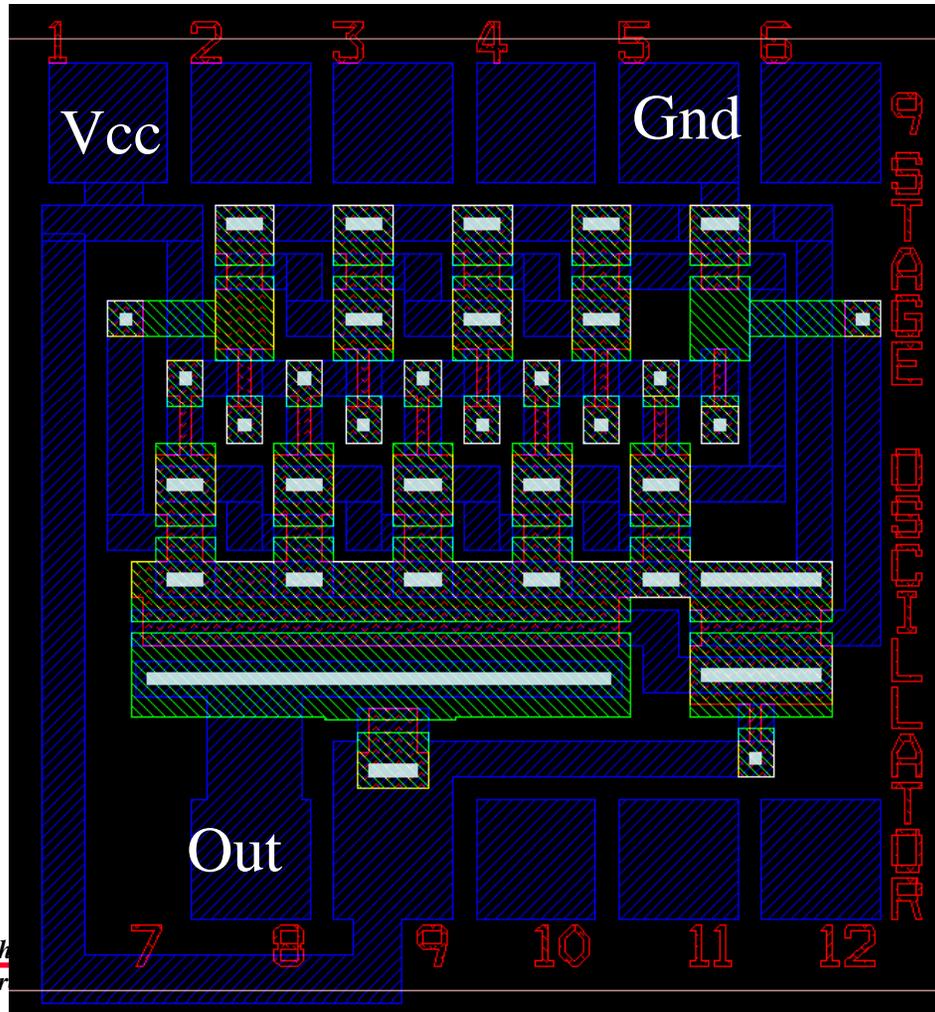
$T$  = period of oscillation



**T = period of oscillation**

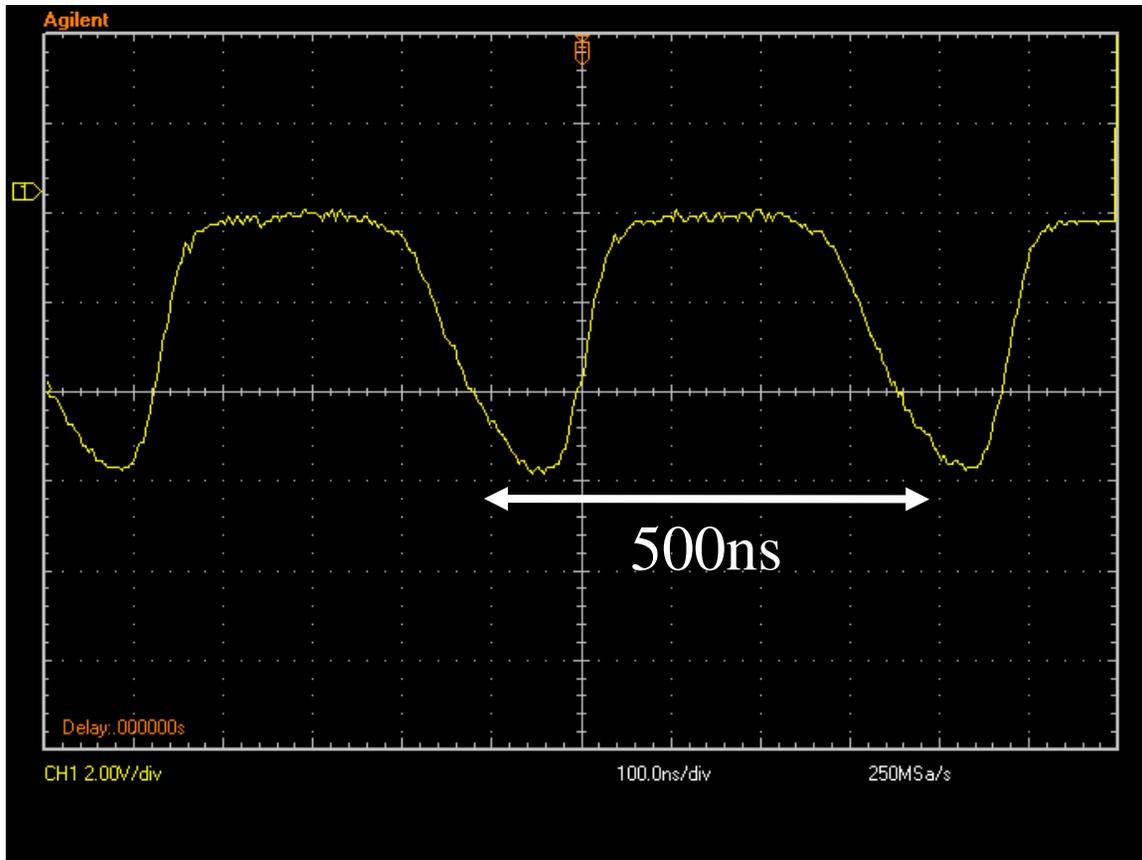


# 9 STAGE RING OSCILLATOR

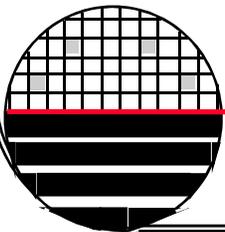


Roch  
Micr

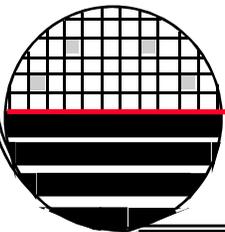
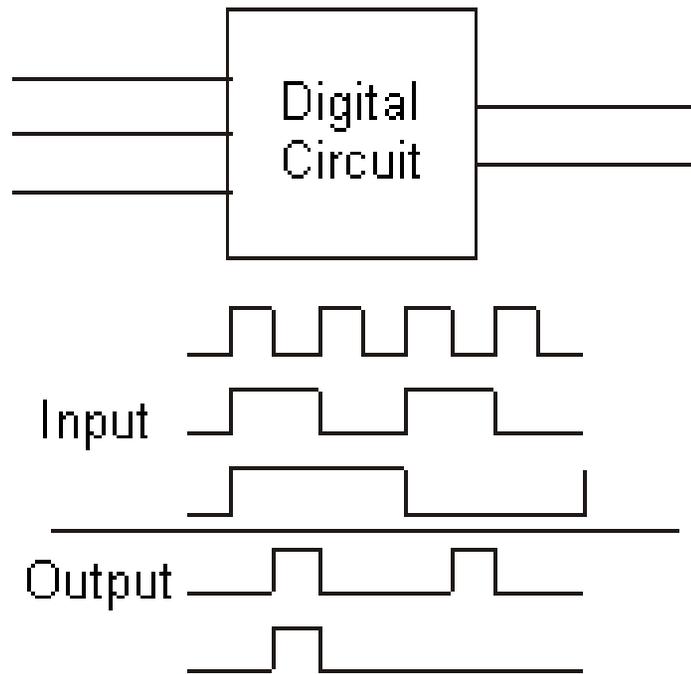
## RING OSCILLATOR OUTPUT



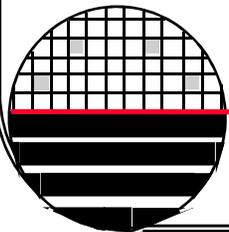
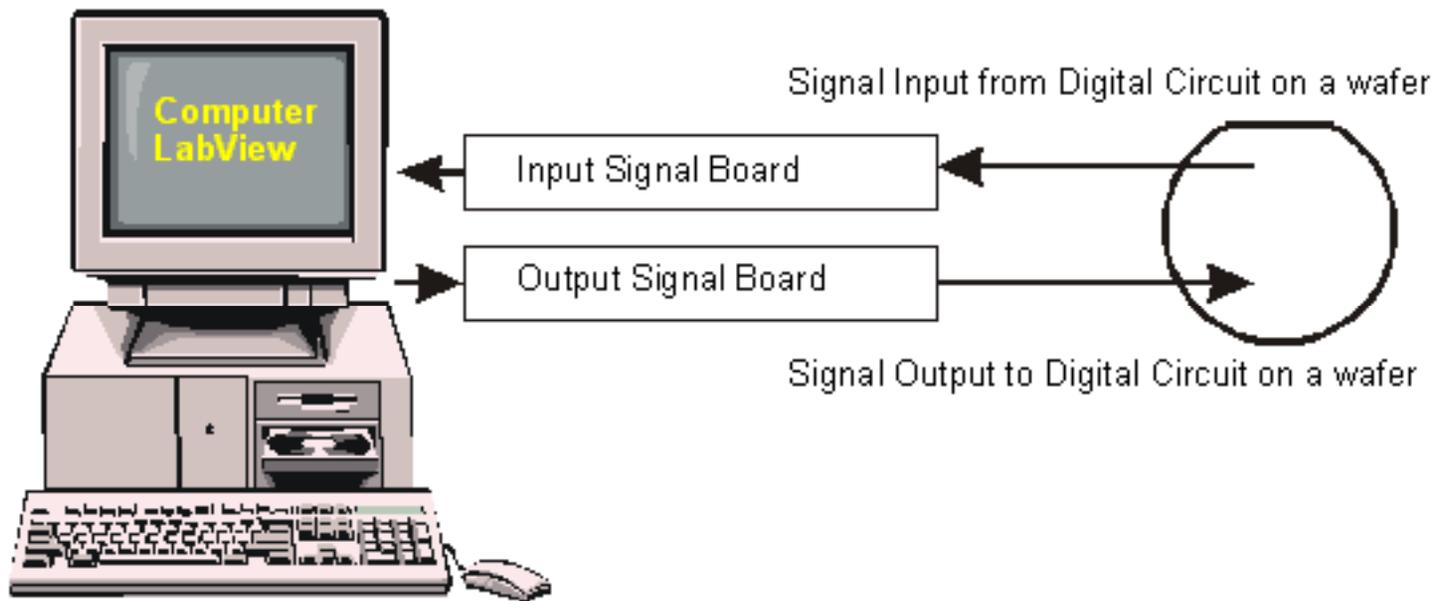
$$\begin{aligned} t_d &= T / 2n \\ &= 500 \text{ ns} / 2 / 9 \\ &= 28 \text{ ns} \end{aligned}$$



**DIGITAL CIRCUIT TESTING**



**LAB VIEW SOFTWARE**



## HARDWARE FOR OUTPUT

AT-AO-6



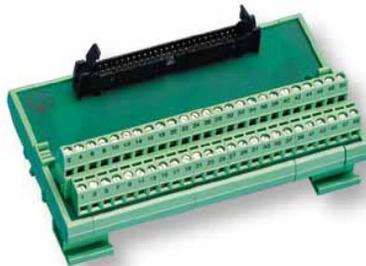
- Available for ISA computers
- 6 analog outputs; 12-bit resolution, 300 kS/s maximum update rate
- 8 digital I/O lines (5 V/TTL)
- 4-20 mA current sinks
- NI-DAQ driver with DAQ channel wizard for reduced configuration

NB1



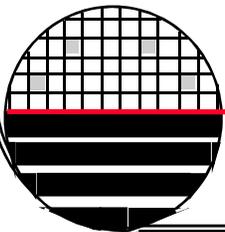
- 50-pin ribbon cable for any board with a 50 pin connector
- Connects to 50pin connector accessories
- 1 m and 2 m length options
- Download PDFs for compatibility charts, more detailed descriptions, and ordering information

CB50



- Low-cost accessory with 50 screw terminals for easily connecting field I/O signals to your DAQ board
- One 50-pin header for directly connecting to 50-pin cables
- Mounts on a standard DIN rail or flush on a wall or panel.
- Dimensions: 13.5 by 7.3 cm (5.3 by 2.9 in.)
- Download PDFs for compatibility charts, more detailed descriptions, and ordering information

## 6 Analog Outputs Ribbon Cable Terminal Board



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## HARDWARE FOR INPUT

AT-MIO-16E-10



- Available for ISA computers
- Up to 16 analog inputs; 12-bit resolution; 100 kS/s sampling rate
- Two 12-bit analog outputs; 8 digital I/O lines; two 24-bit counters
- Calibration certificate included for NIST traceability
- NI-DAQ driver with DAQ channel wizard for reduced configuration

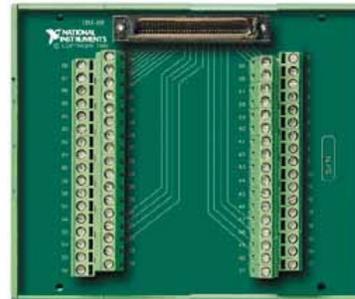
## 16 Analog Inputs Ribbon Cable Terminal Board

R6868

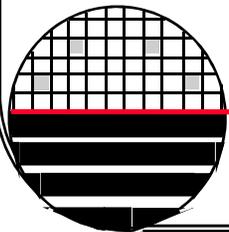


- 68-pin flat ribbon cable terminated with two 68-pin connectors
- 1 m length available
- Download PDFs for compatibility charts, more detailed descriptions, and ordering information

TBX-68

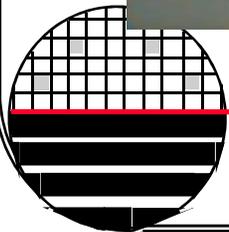


- Termination accessory with 68 screw terminals
- Easy connection of field I/O signals to 68-pinDAQ devices
- Mounted in plastic base; includes hardware for mounting on a standard DIN rail
- Dimensions: 12.50 by 10.74 cm (4.92 by 4.23 in.)
- Download PDFs for compatibility charts, more detailed descriptions, and ordering information



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*FINAL SYSTEM*

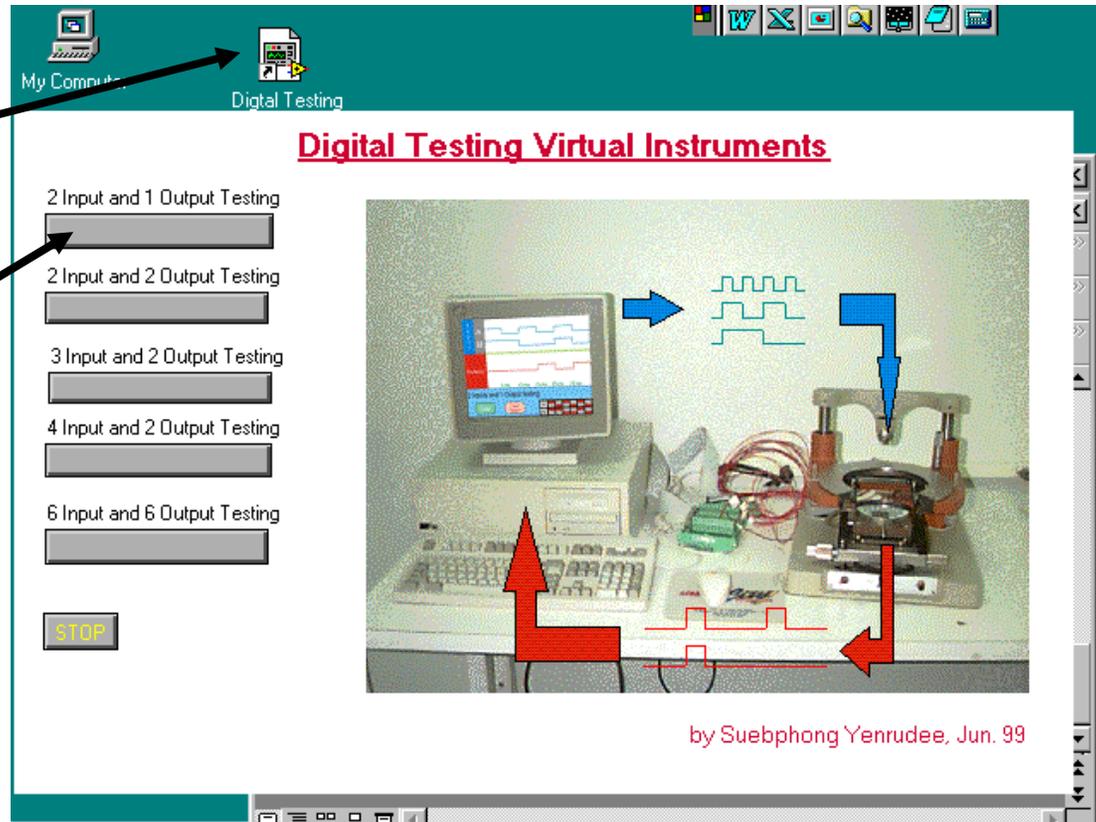


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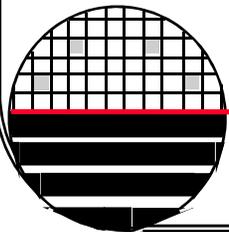
***CUSTOM SOFTWARE INTERFACE***

Click on digital testing icon to invoke the lab view software and this main menu.

Click to select the type of test you wish to run.



**MAIN MENU**



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# NOR GATE AND NOR FLIP FLOP

## PMOS 2 INPUT NOR

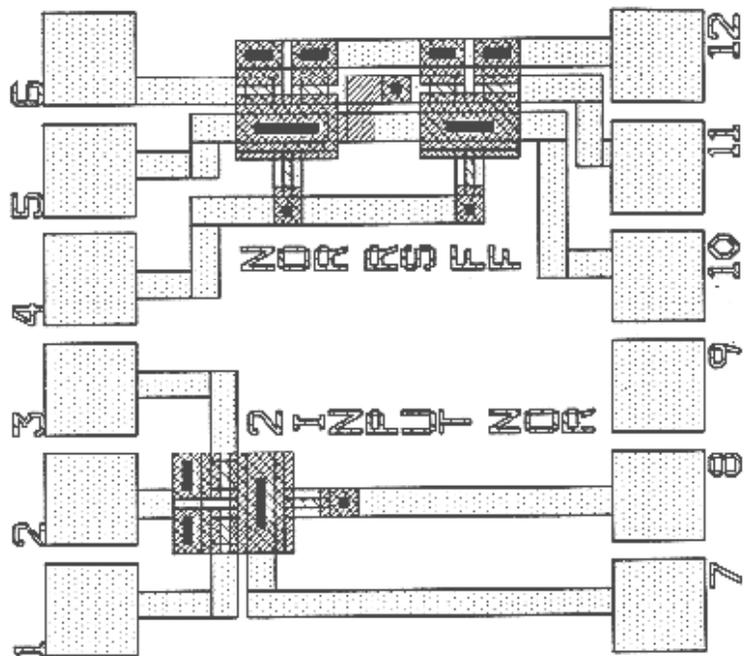
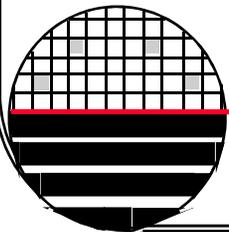
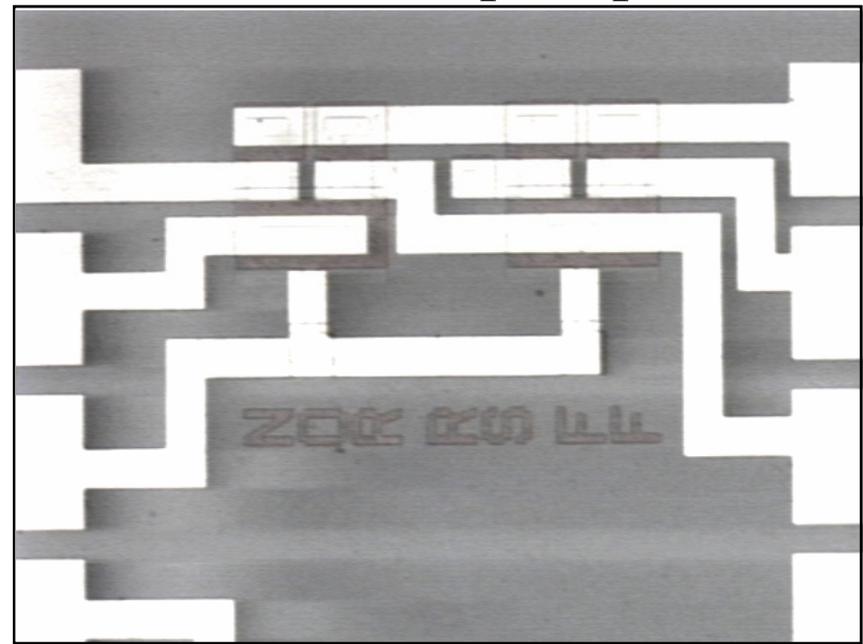
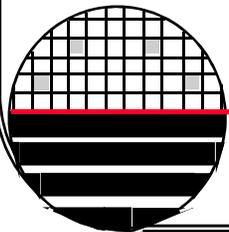
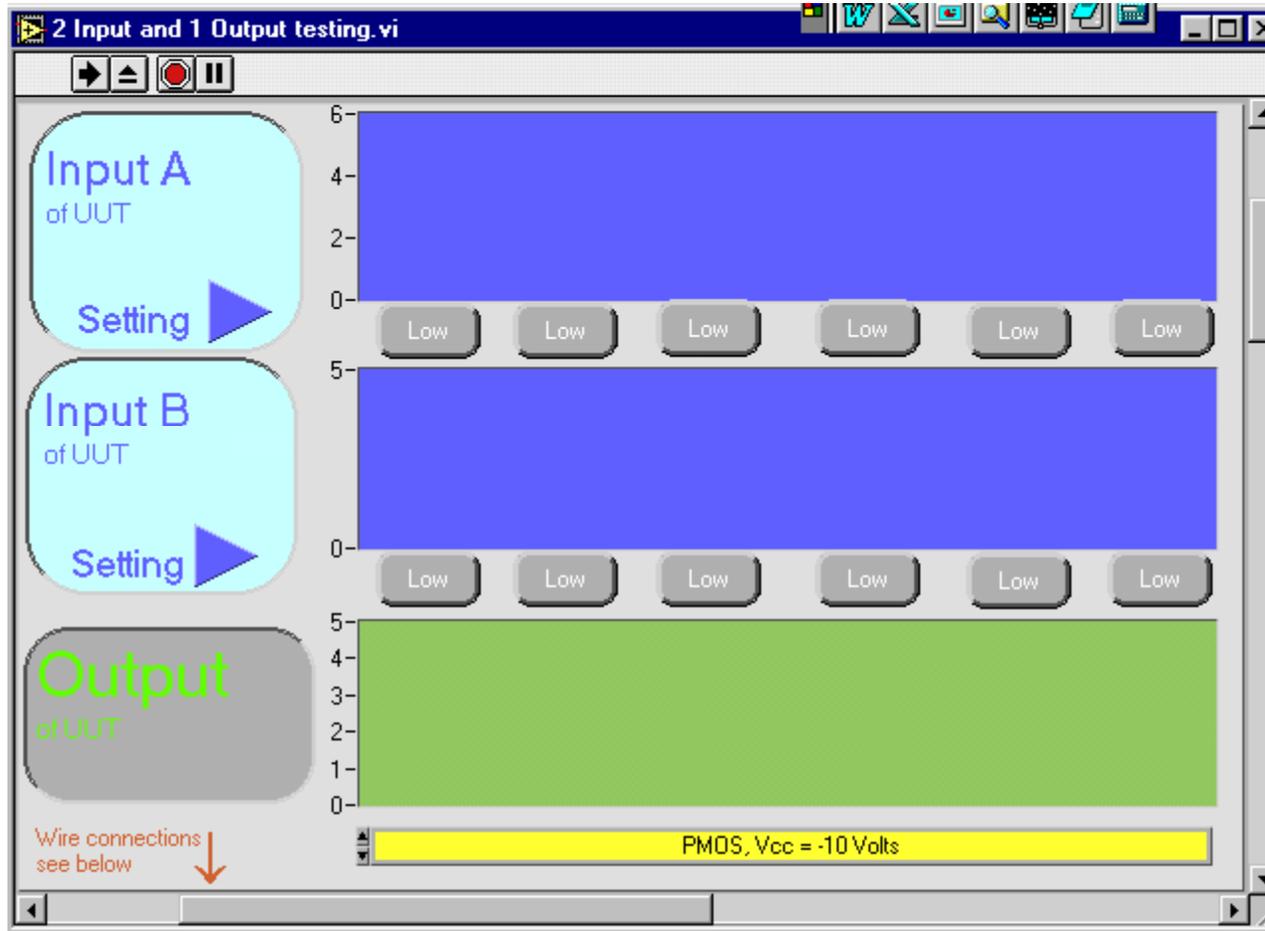


Figure 7 DIGITAL DEVICES

## PMOS NOR RS Flip Flop



**TESTING TWO INPUT ONE OUTPUT LOGIC GATES**



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***FOUR CHOICES FOR SUPPLY VOLTAGES***

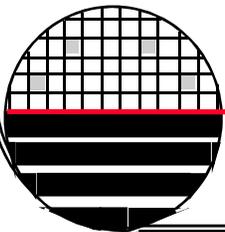
CLICK TO SELECT ONE

PMOS,  $V_{cc} = -10$  Volts

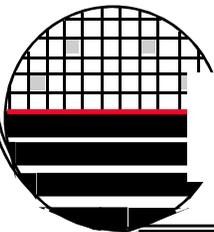
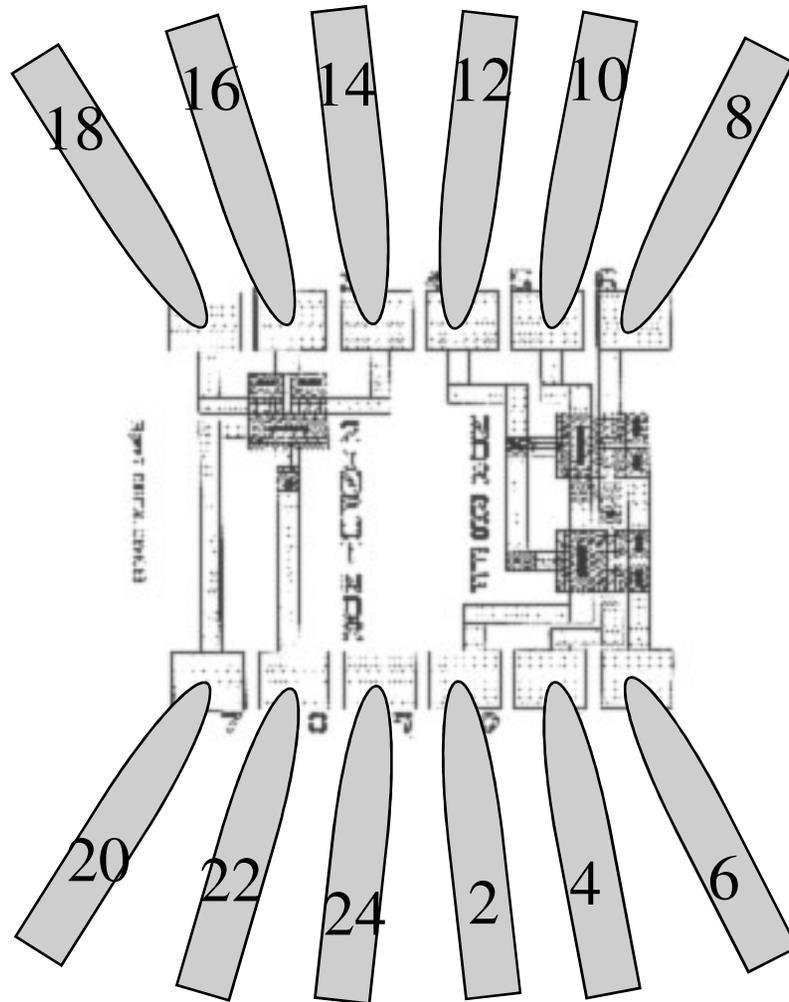
**CMOS/TTL  $V_{cc} = +5$  Volts**

NMOS,  $V_{cc} = +10$  Volts

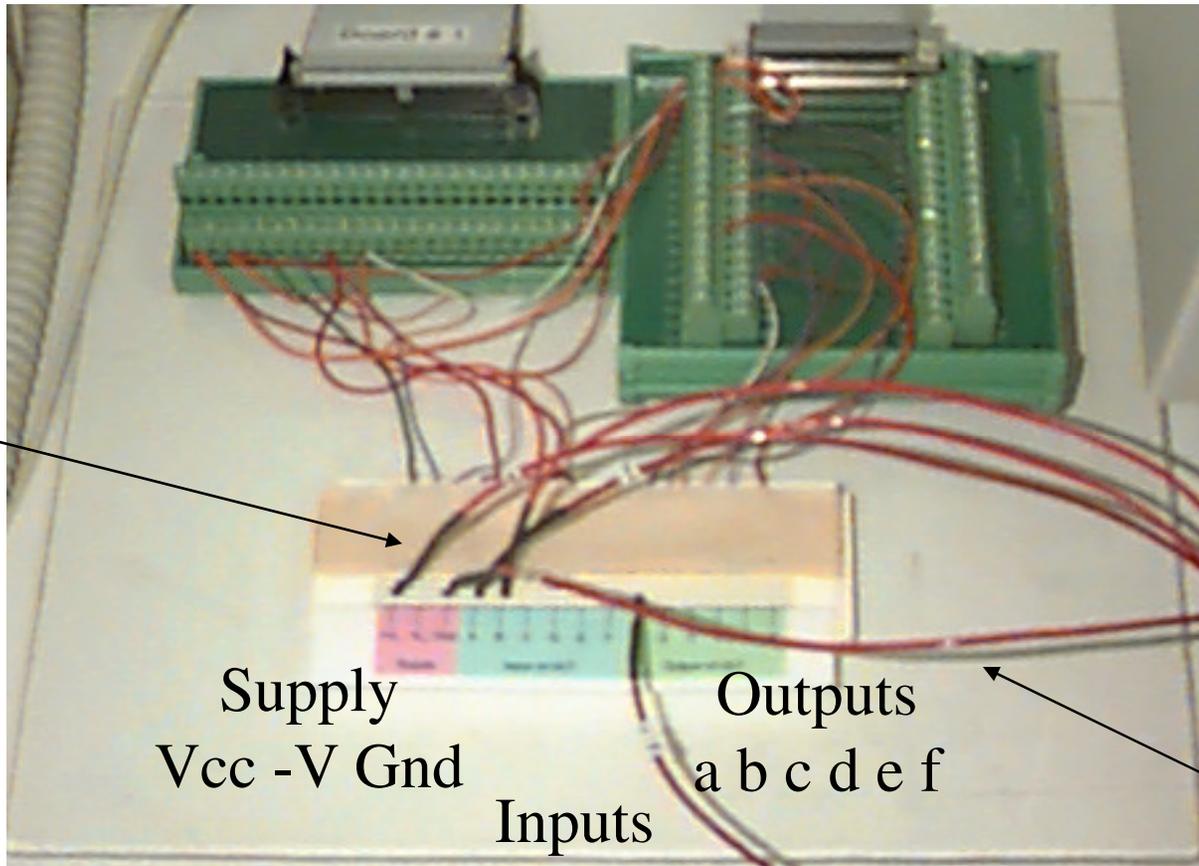
ANALOG,  $V_{cc} = +5$  Volts,  $V_{dd} = -5$  Volts



***PROBE CARD/WIRE CONNECTIONS***



**SWITCH MATRIX (MANUAL)**



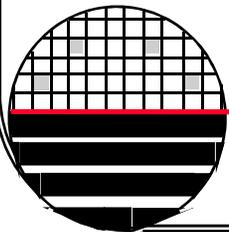
Wire #17

Supply  
Vcc -V Gnd

Inputs  
a b c d e f

Outputs  
a b c d e f

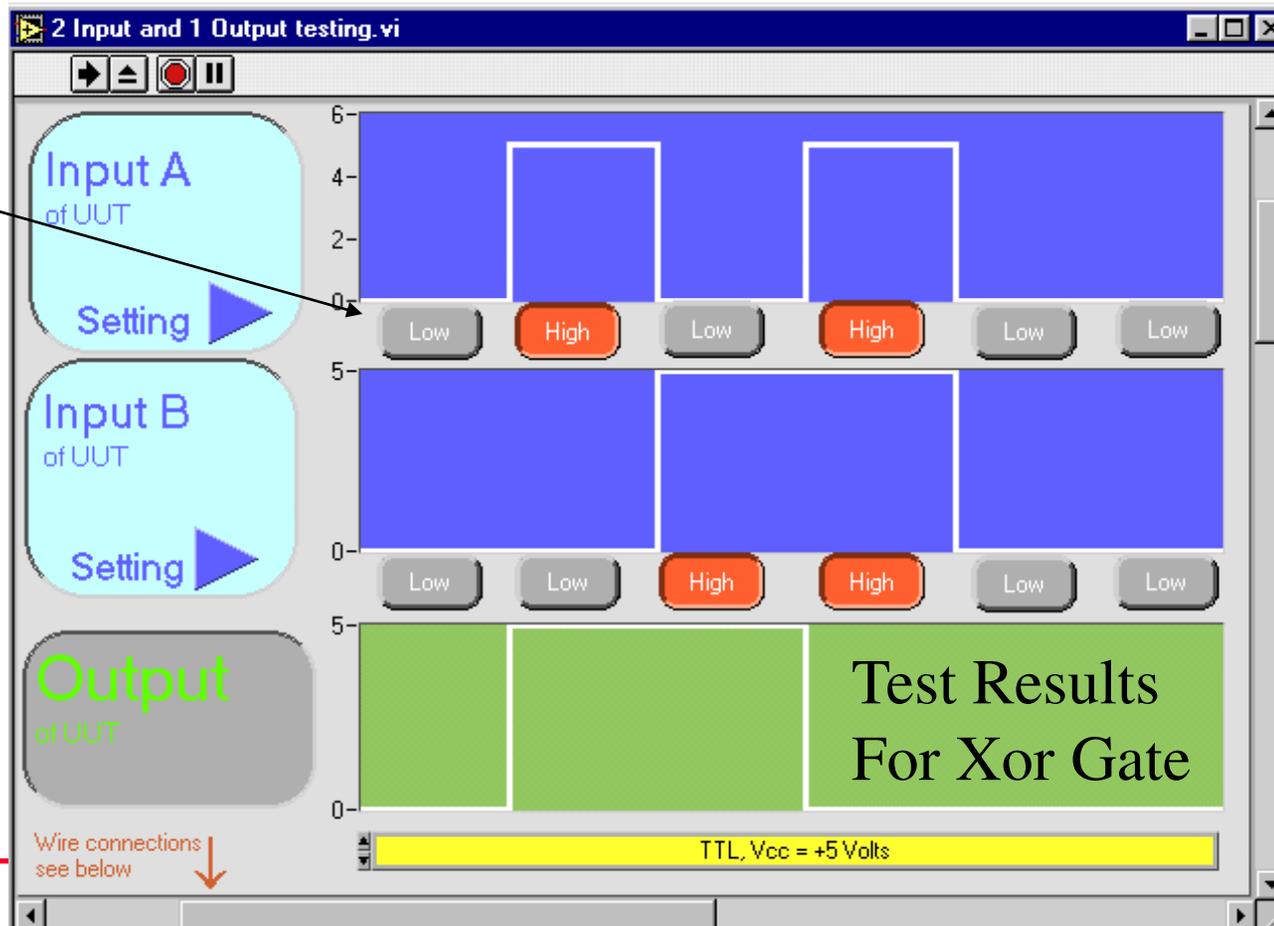
Wire #8



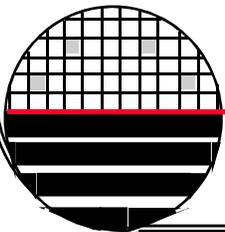
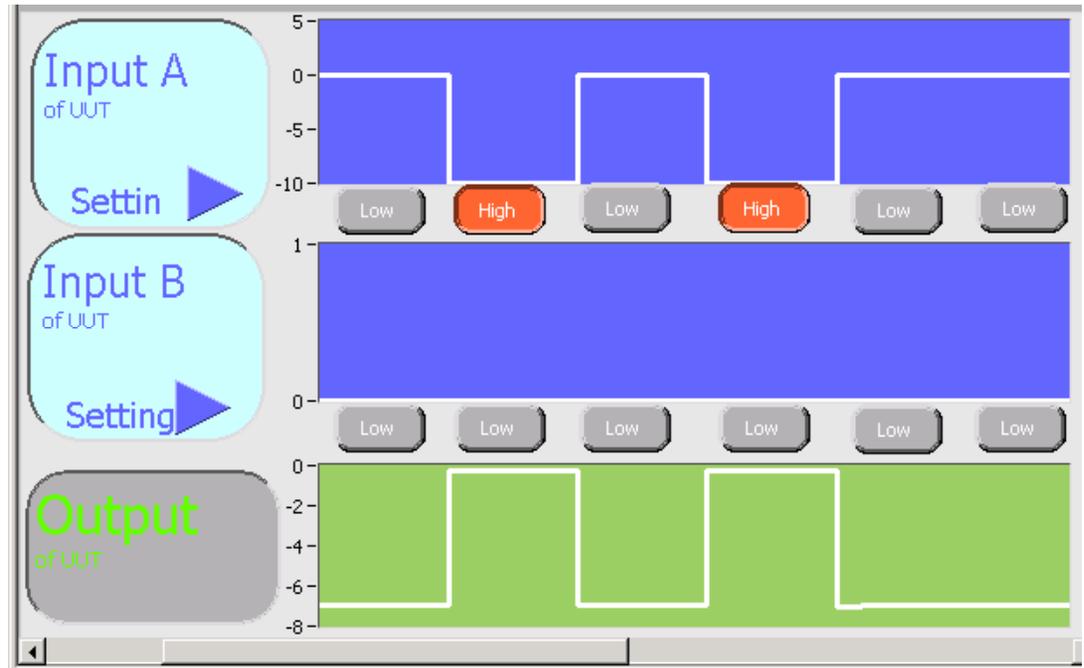
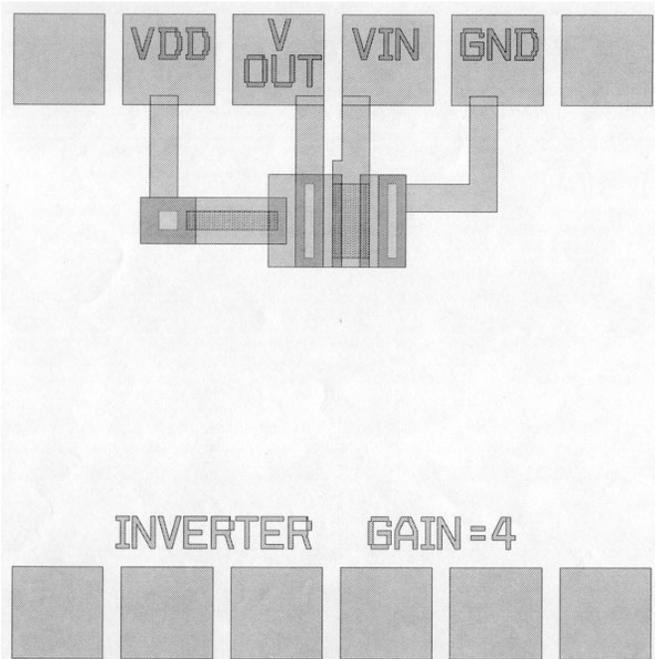
***RUN TEST***

Click to Start Test  
Stop Test

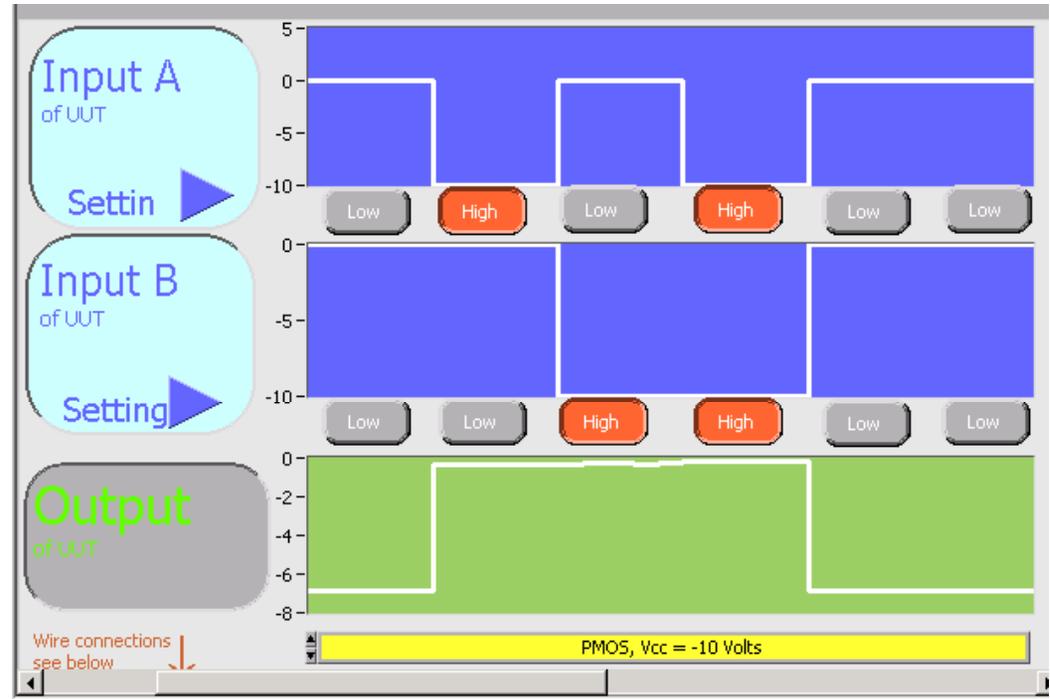
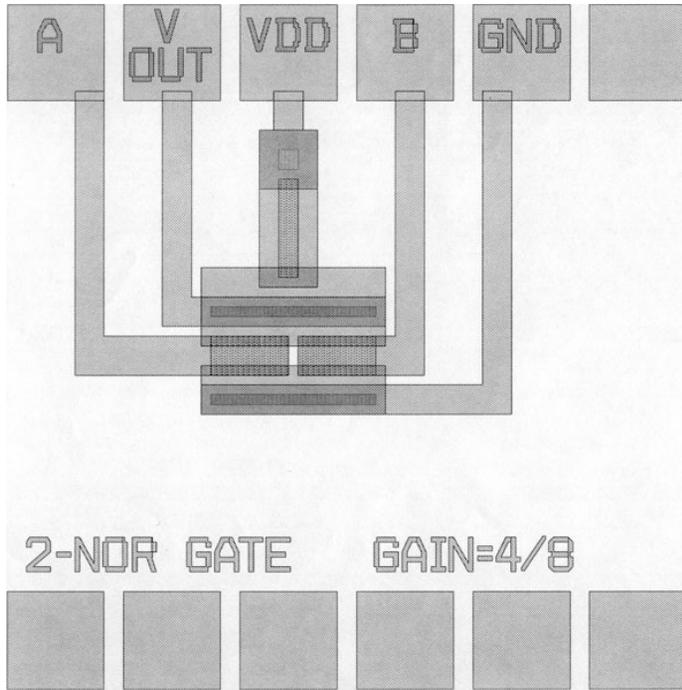
Click to  
Select  
When  
Output is  
High or  
Low



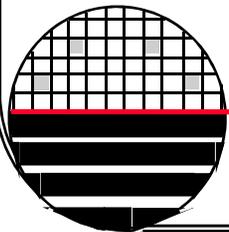
**PMOS INVERTER GAIN=4**



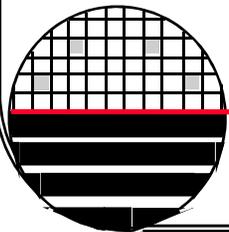
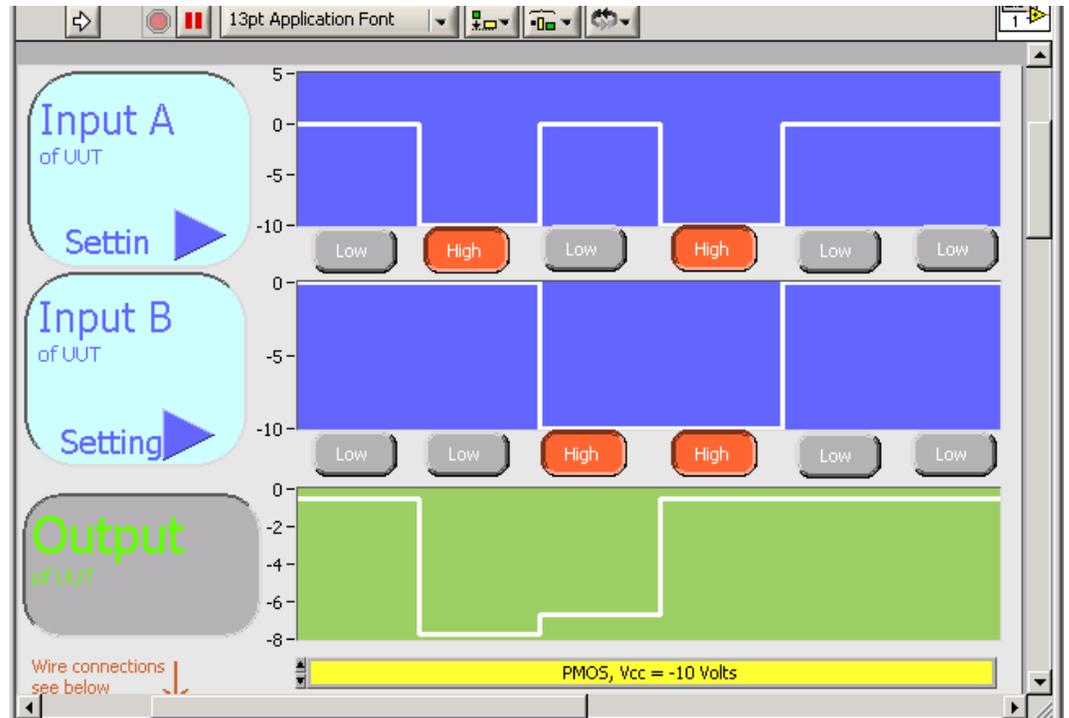
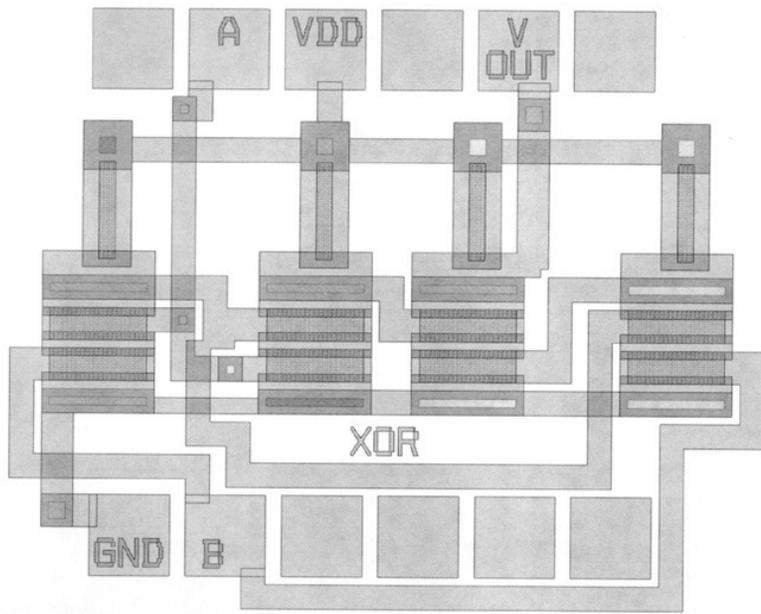
**PMOS 2-INPUT NOR**



Test for PMOS Two Input NOR, Gain = 4 or 8



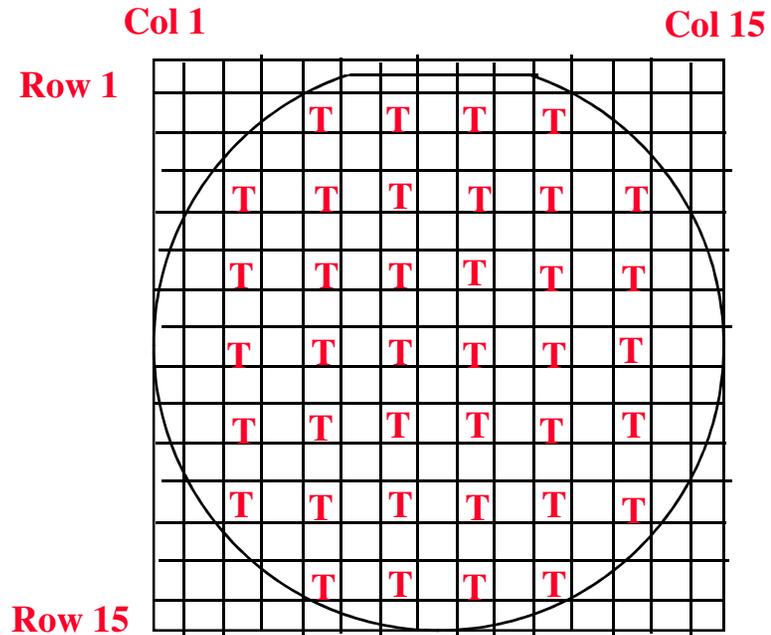
**PMOS 2-INPUT XOR**



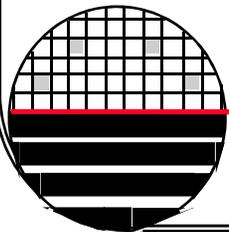
**WAFER MAPS FOR MESA**

```

nmos Vt target +1
000000000000000000
0000505050500000
000000000000000000
005060507050700
000000000000000000
004040304030300
000000000000000000
004040404040400
000000000000000000
004050405090600
000000000000000000
005050606060700
000000000000000000
0000505050500000
000000000000000000
    
```



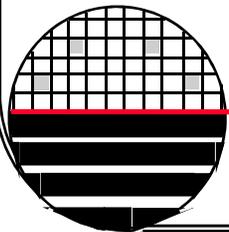
row 1 is the first row in which a full die is located  
 column 1 is the first column in which a full die is located



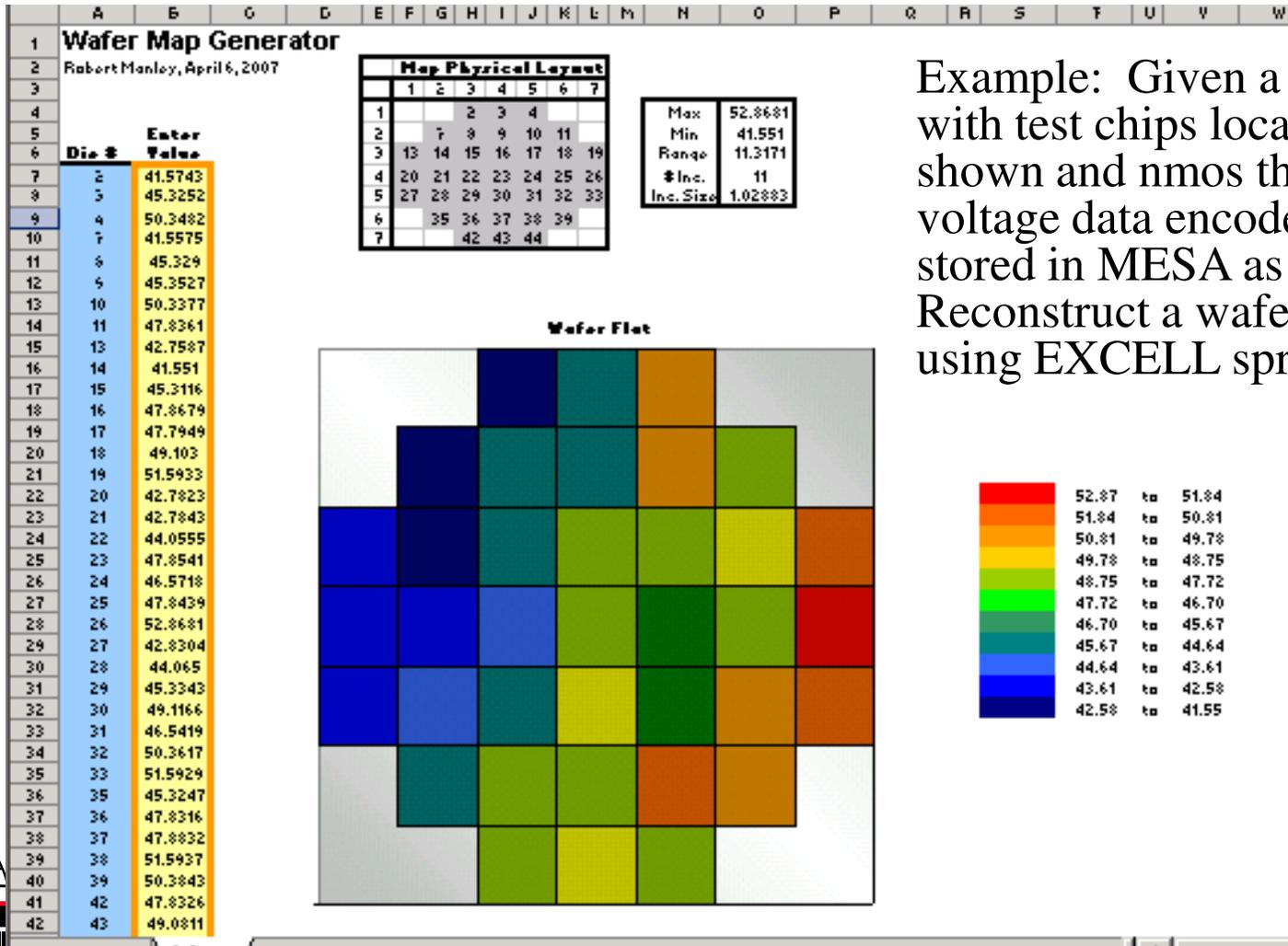
## WAFER MAPS FOR MESA

### Code

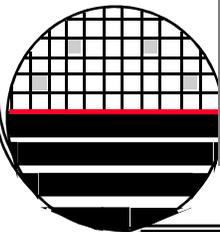
0	no die
1	value<(Target-40%)
2	(Target-40%)<value<(Target-30%)
3	(Target-30%)<value<(Target-20%)
4	(Target-20%)<value<(Target-10%)
5	(Target-10%)<value<(Target+10%)
6	(Target+10%)<value<(Target+20%)
7	(Target+20%)<value<(Target+30%)
8	(Target+30%)<value<(Target+40%)
9	(Target+40%)<value



WAFER MAP

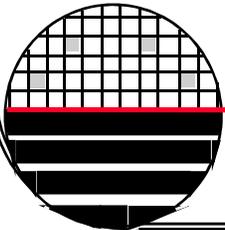


Example: Given a wafer with test chips located as shown and nmos threshold voltage data encoded and stored in MESA as shown. Reconstruct a wafer map using EXCELL spreadsheet.



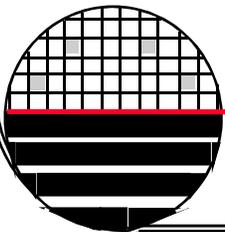
***FUTURE WORK***

- **More Automation**
- **Improved Wafer Mapping**
- **More Complete Testing**



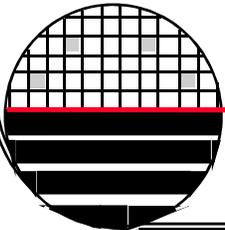
## ***CONCLUSION***

- **A test specification has been developed**
- **A history data base has been developed**
- **Testing is very time consuming. It takes us 9 hours to do all the specified tests and even then we only test a few devices on a wafer.**
- **Currently we test about 1% of the devices**



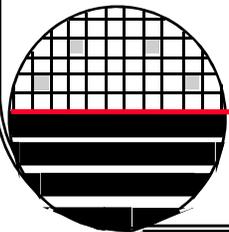
## REFERENCES

1. LabView Software, National Instruments,  
<http://www.natinst.com>

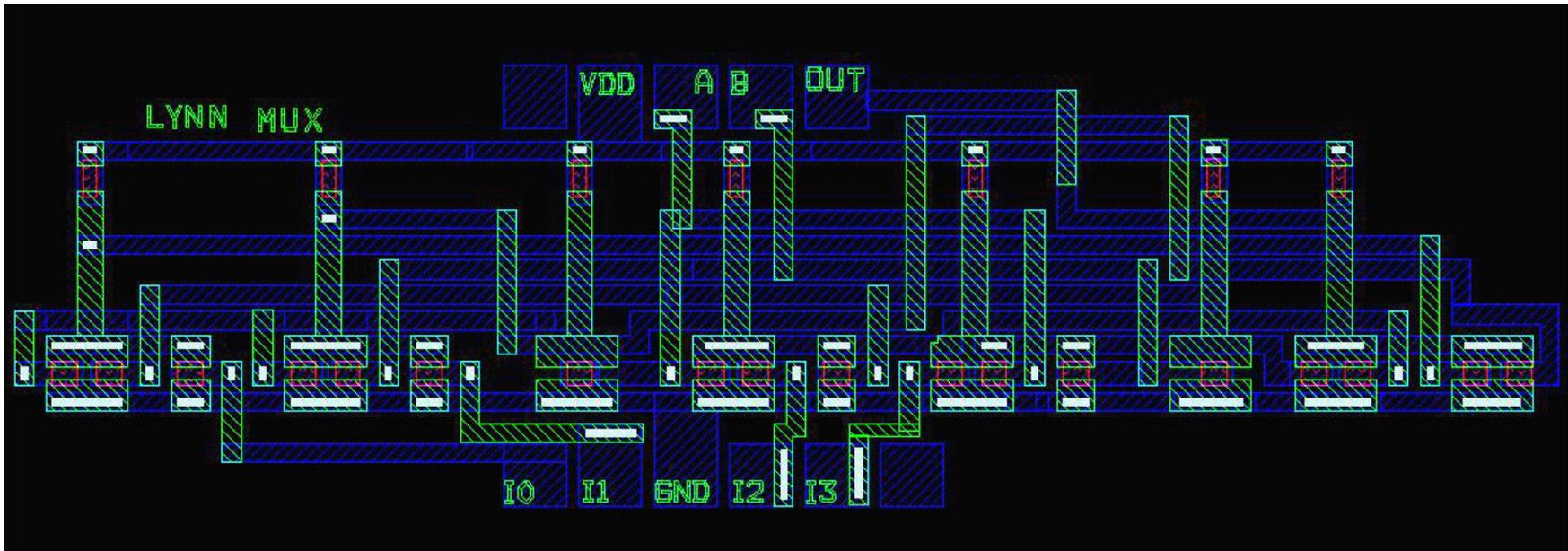


***REVIEW QUESTIONS - PMOS TEST SPECIFICATION***

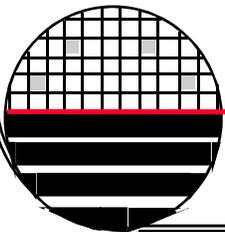
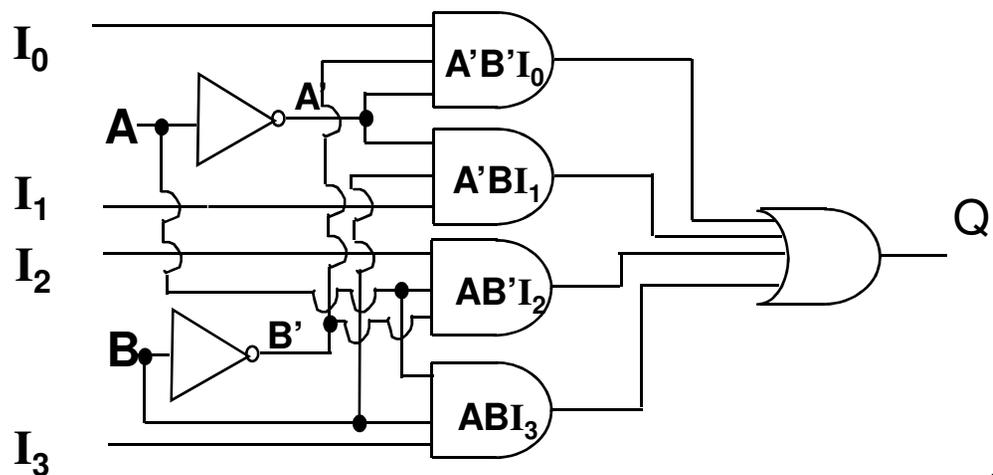
1. How is  $V_t$  and  $g_m$  found from the transistor family of curves.
2. Is the  $V_t$  and  $g_m$  the same in the non-saturation region as in the saturation region?
3. What is the significance of the sub-threshold slope. What is the difference between sub-threshold slope and sub-threshold swing?
4. What is the significance of the noise margin.
5. What is the purpose of the ring oscillator test structure.



# MUX LAYOUT AND GATE LEVEL SCHEMATIC

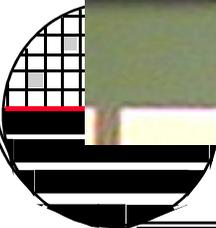
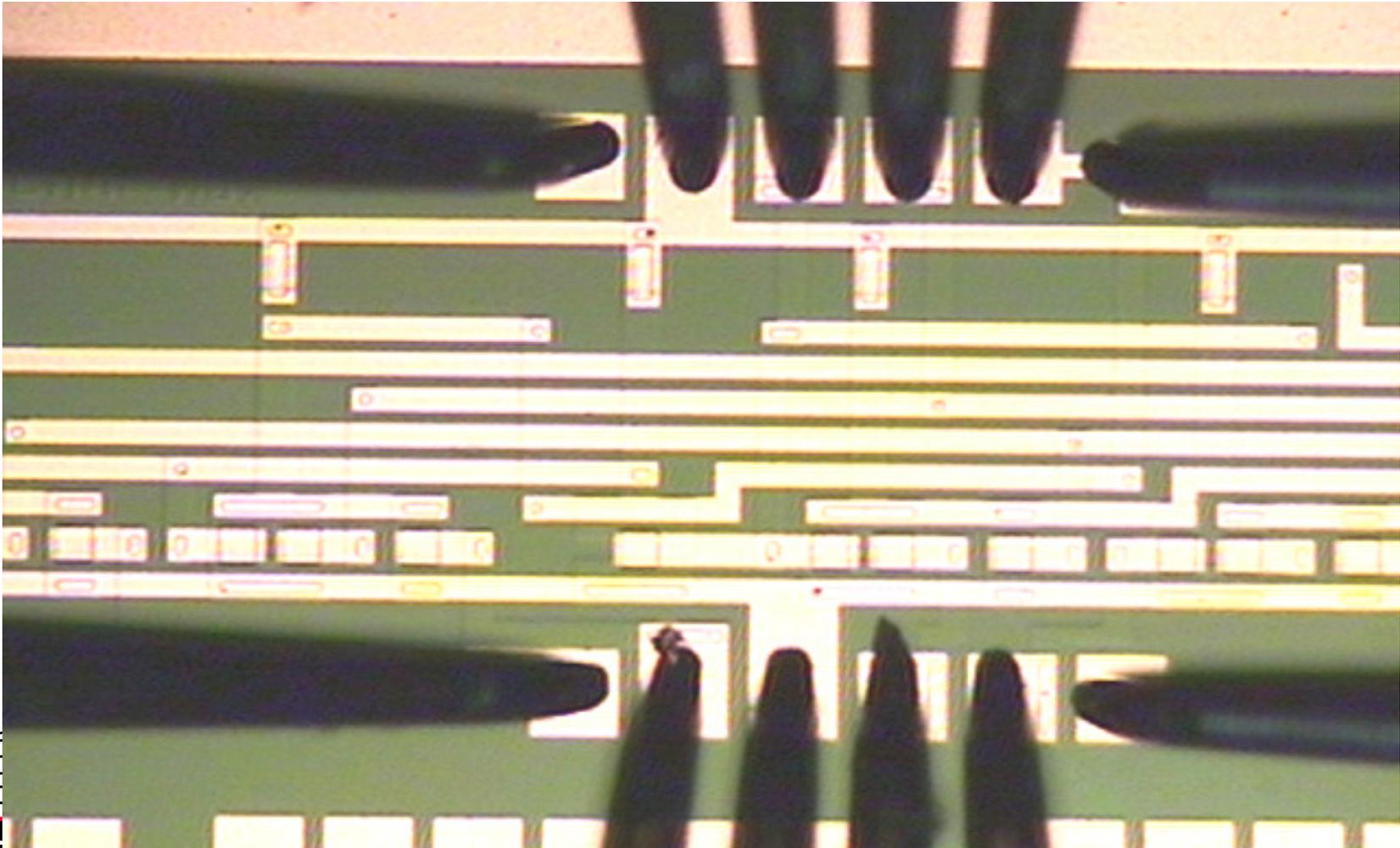


25 Transistors

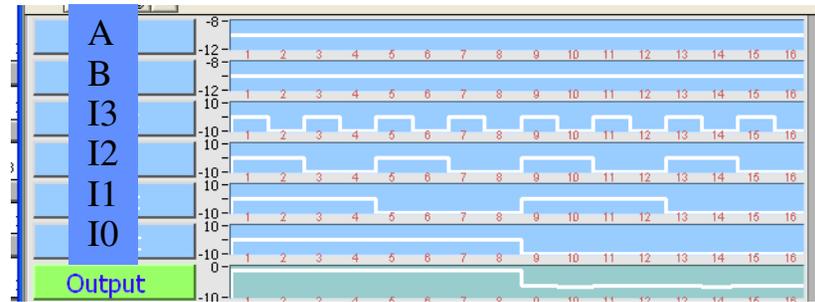
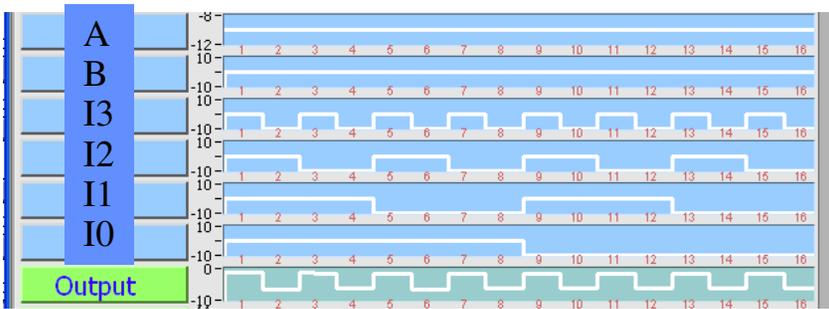


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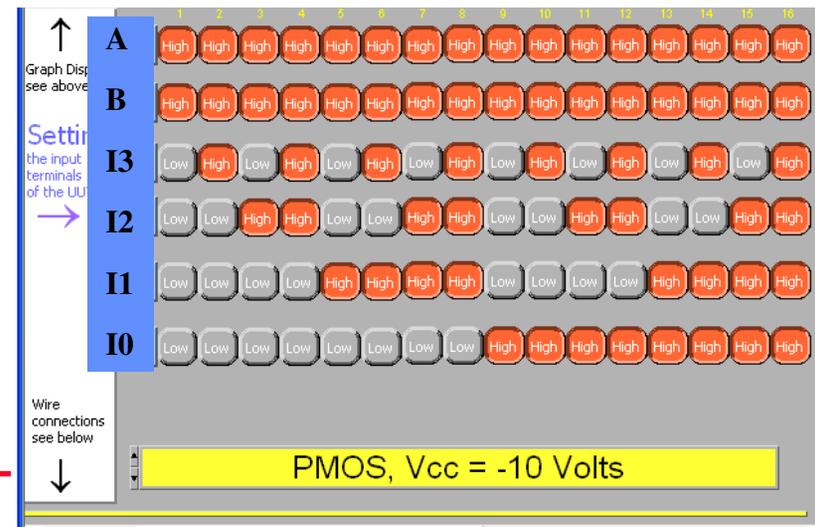
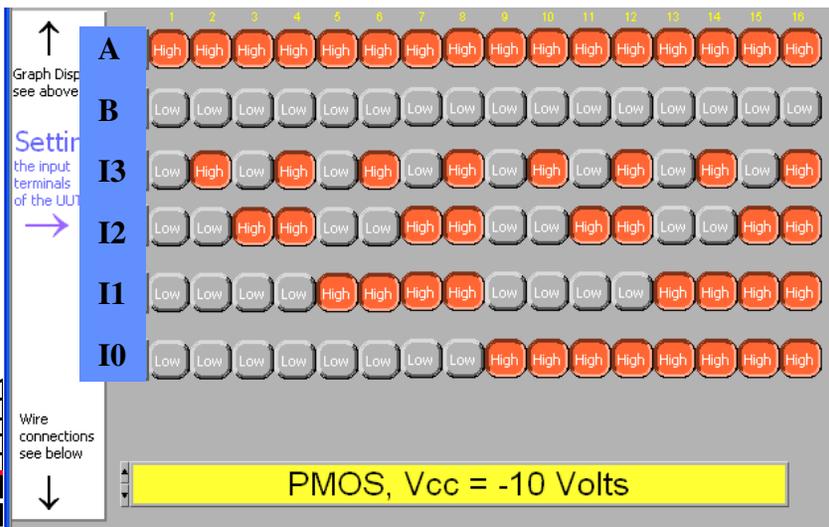
*PMOS 4-INPUT MULTIPLEXER*



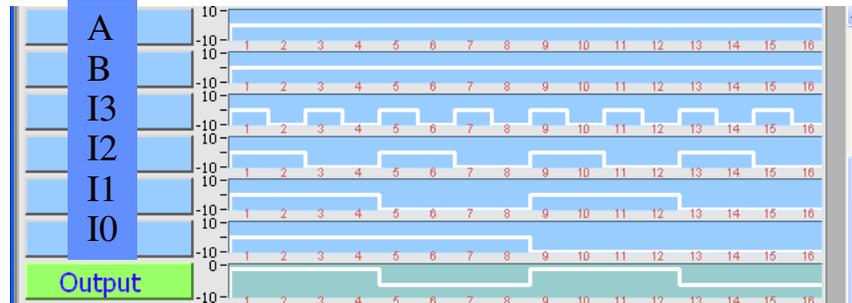
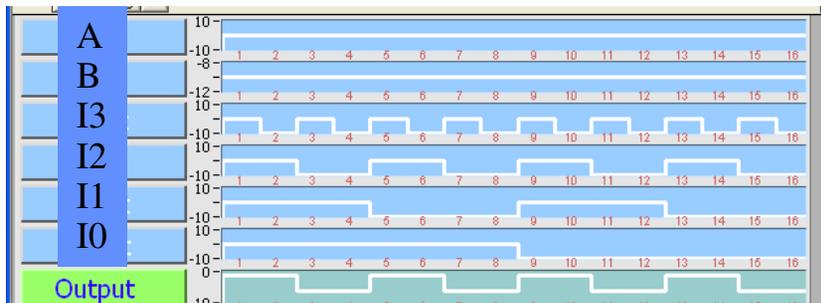
**MUX TEST RESULTS**



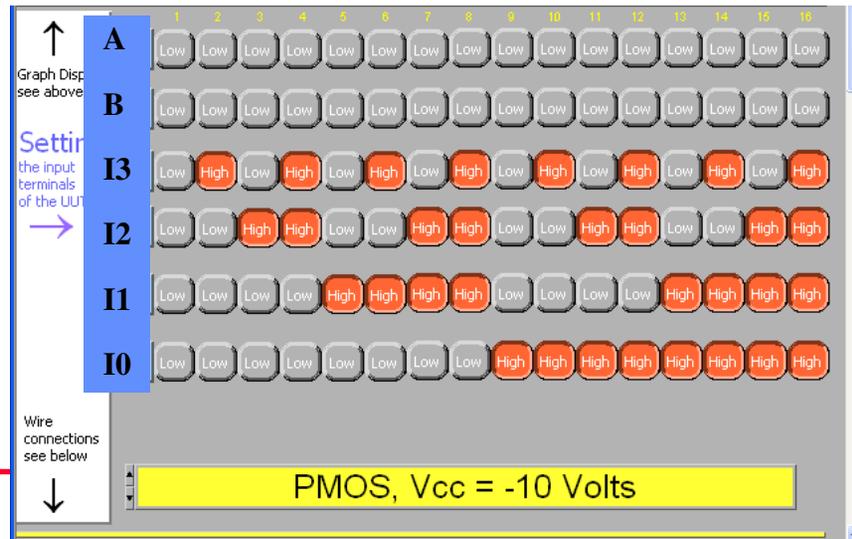
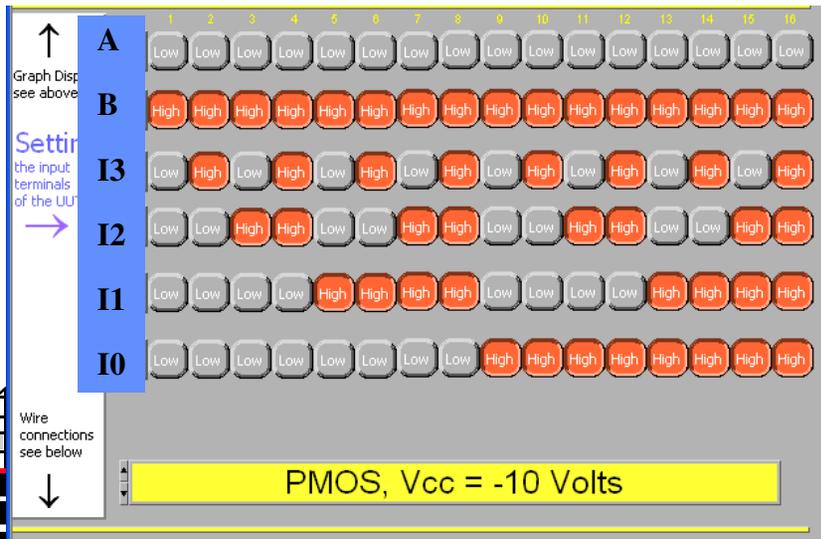
In PMOS logic low is 0 volts, logic high is  $-V_{cc}$



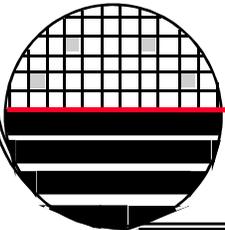
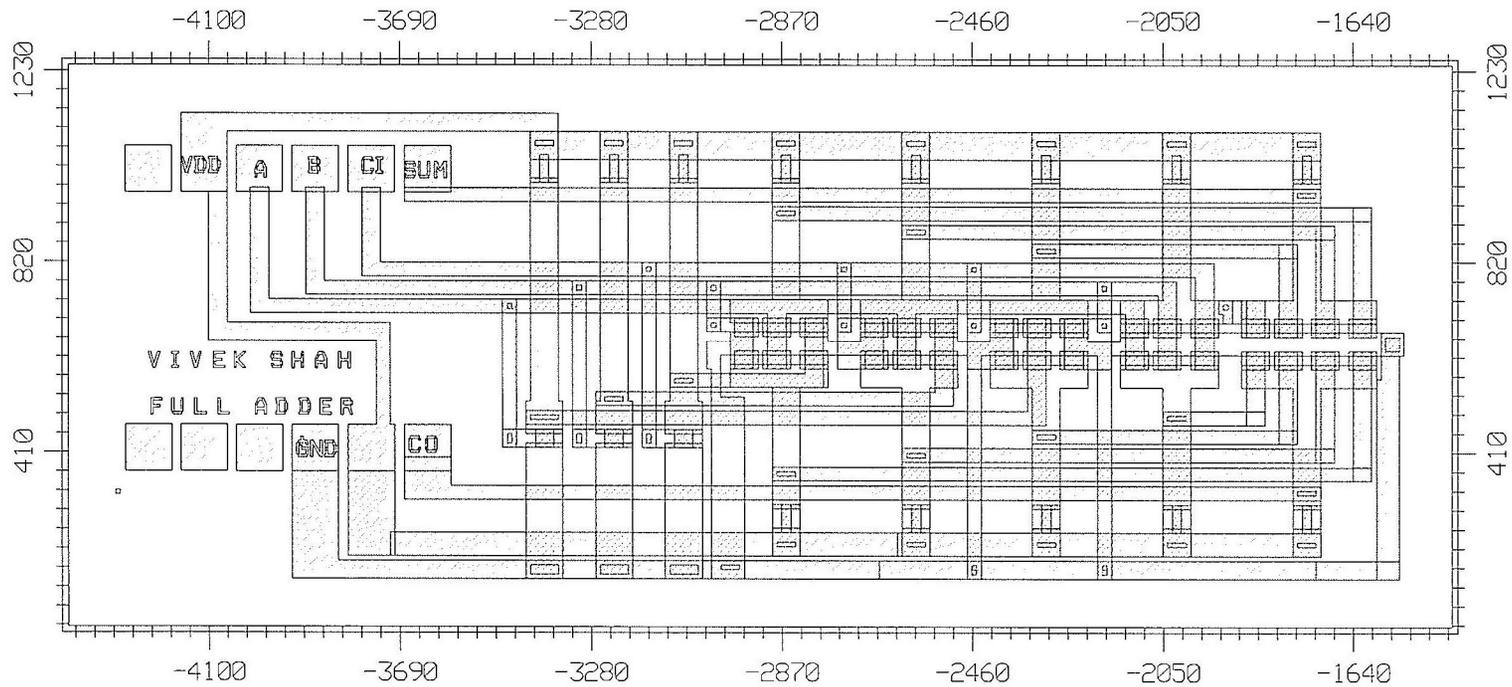
**MUX TEST RESULTS**



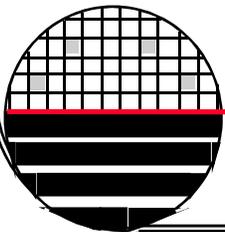
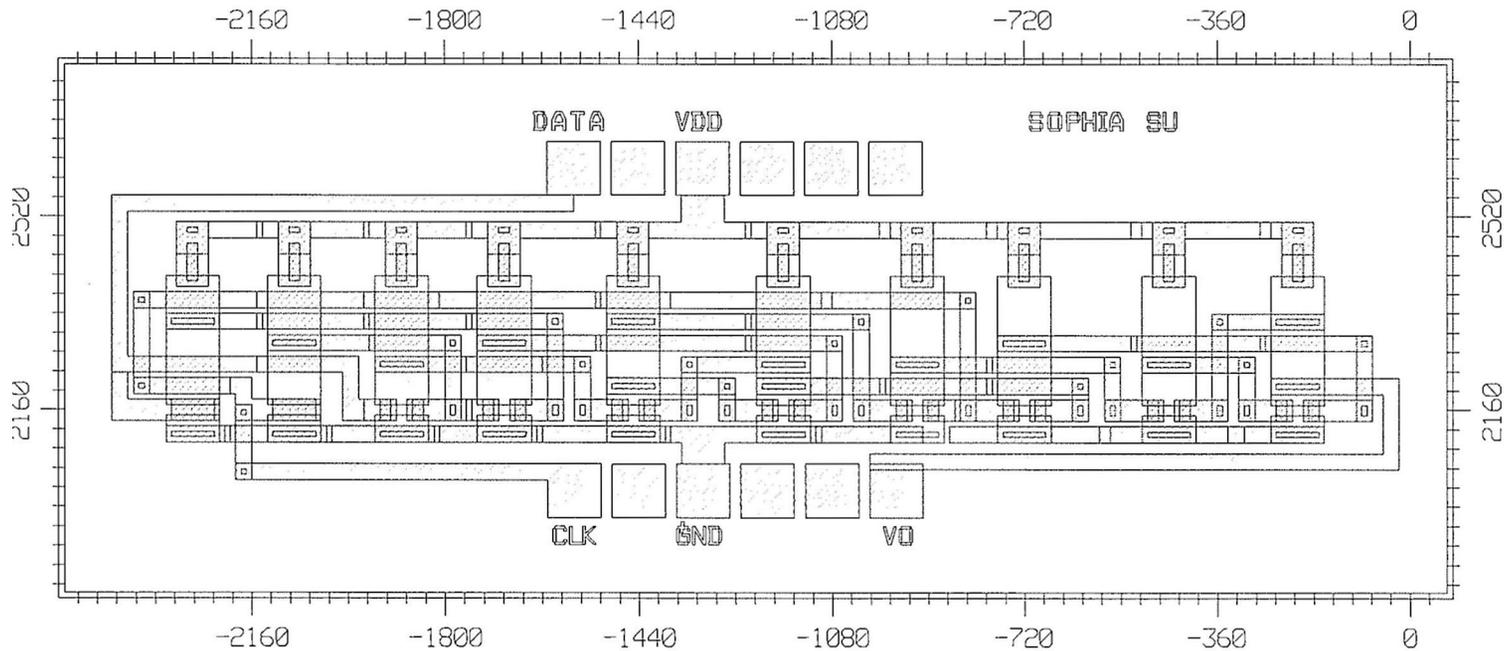
In PMOS logic low is 0 volts, logic high is  $-V_{cc}$



**PMOS FULL ADDER**

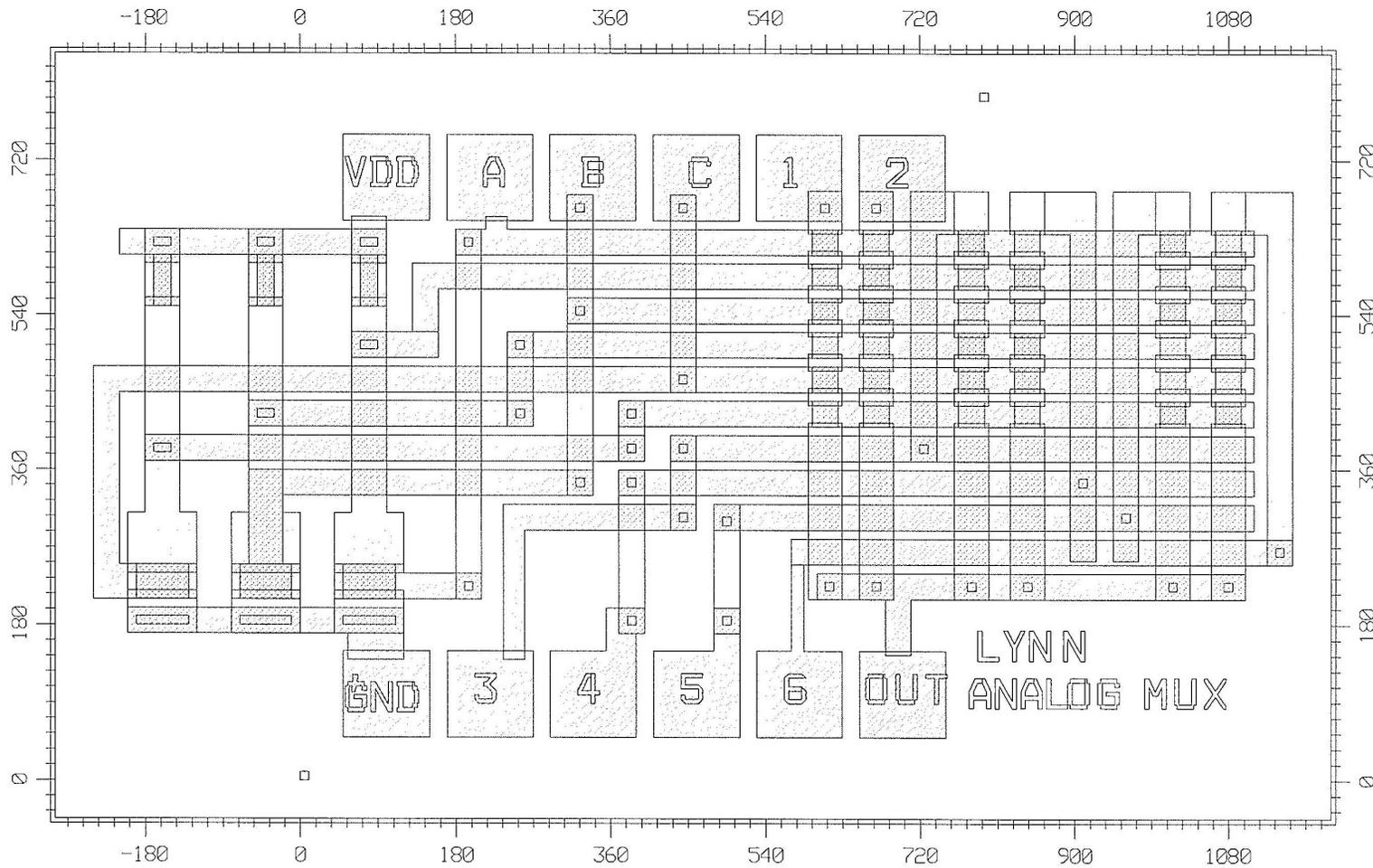


**PMOS CLOCKED DATA LATCH**



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**PMOS ANALOG MUX**



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